

Design Example Report

300 W Forward Power Supply Using HiperPFS TM -3 PFS7528H and HiperTTFS7706H	
Specification	90 VAC – 264 VAC Input; 280 W (61 V (Nom.) at 0 – 4.59 A) CV/CC Output; 20 W (5 V / 4 A) Standby Output
Application	Battery Charger
Author	Applications Engineering Department
Document Number	DER-484
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Revision	1.2

Summary and Features

- Integrated forward power stage and flyback standby for a very low component count design
- 90-264 VAC input range with PFC
- >87% full load efficiency
- Compact size
- >0.96 PF at 20% load
- Low no-load input power
- Excellent CV regulation
- Excellent CC regulation

PATENT INFORMATION

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Tá	able of Co	ntents	
1	Introduc	tion	4
2	Power Si	upply Specification	. 5
3	Schemat	ic	. 6
4	Circuit D	escription	. 8
	4.1 Inpu	ut Filter / Boost Converter	8
	4.1.1	Input EMI Filter and Rectifier	8
	4.1.2	PFS7528H Boost Converter	. 8
	4.1.3	Input Feed Forward Sense Circuit	
	4.1.4	Output Feedback	9
		n Forward Converter / Standby	
	4.3 Prim	nary Bias Supply	11
		n Output Rectification	
		put Current and Voltage Control	
		ndby Output	
		ondary Bias Supply	
5		out	
6		aterials	
7	_	CS	
		Boost Inductor (L3) Specification	
	7.1.1	Electrical Diagram	
	7.1.2	Electrical Specification	
	7.1.3	Material List	
	7.1.4	Build Diagram	
	7.1.5	Winding Illustrations	
		n Transformer (T1) Specification	
	7.2.1	Electrical Diagram	
	7.2.2	Electrical Specifications	
	7.2.3	Material List	
	7.2.4	Build Diagram	
	7.2.5	Winding Instructions	
	7.2.6	Winding Illustrations	
		ndby Transformer (T2) Specification	
	7.3.1	Electrical Diagram	
	7.3.2	Electrical Specifications	
	7.3.3	Material List	
	7.3.4	Build Diagram	
	7.3.5	Winding Instructions	
	7.3.6	Transformer Illustrations	
		1 Output Choke (L4) Specification	
	7.4.1	Electrical Diagram	
	7.4.2	Material List	
	7.4.3	Winding Illustration	35



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8 PFC Design Spreadsheet	
10 Main / Standby Design Spreadsheet	. 41
11 Heat Sinks	
11.1 Main Primary Heat Sink (U1 and BR1)	
11.2 Primary Heat Sink #2 (U2)	
11.3 Secondary Heat Sink	
Performance Data	. 58
12.1 Output Load Considerations for Testing a CV/CC Supply in Battery Charger	
Applications	. 58
12.2 Efficiency	
12.3 No-Load Input Power	. 60
12.4 Power Factor	
12.5 Main Output V-I Characteristic	
12.5.1 V-I Characteristic, Constant Resistance Load	
12.5.2 Main Output V-I Characteristic, Constant Voltage Load	
13 Waveforms	
13.1 Primary Voltage and Current, Main and Standby Converters	
13.2 AC Input Voltage and Current	
13.3 PFC Stage Inductor Current / Drain Voltage Waveforms	. 66
13.4 Output Rectifier Peak Reverse Voltage	
13.5 Main Start-up Output Voltage / Current and Transformer Primary Current Usin	ng
Constant Voltage and Constant Voltage Output Loads	
13.5.1 Main and Standby Start-Up, Supply Started via AC Input	. 68
13.5.2 Main Output Start-Up Using Enable Switch	
13.6 Load Transient Response, Voltage Mode 50%-75%-50% Load Step	
14 Output Ripple Measurements	
14.1 Ripple Measurement Technique	
14.2 Output Ripple Measurements	
15 Temperature Profiles	
15.1 Spot Temperature Measurements	
15.1.1 90 VAC, 60 Hz, 100% Load Overall Temperature Profile	
16 Gain-Phase	
16.1 Main Output Constant Voltage Mode Gain-Phase	. 78
16.2 Main Output Constant Current Mode Gain-Phase	. 79
17 Conducted EMI	. 80
17.1 Conducted EMI Scan	. 81
18 Revision History	. 83

Important Notes:

Although this board is designed to satisfy safety isolation requirements, the engineering prototype has not been agency approved. All testing should be performed using an isolation transformer to provide the AC input to the prototype board.

1 Introduction

This engineering report describes a 61 V (nominal), 280 W power supply reference design operating from 90-264 VAC. A 5 V, 4 A standby output is also provided. The power supply main output is designed with a constant voltage/ constant current characteristic for use in battery charger applications.

The design is based on the PFS7528H and TFS7707H, with the main forward stage operating at 66 kHz.



Figure 1 - DER-484 Photograph, Top View.

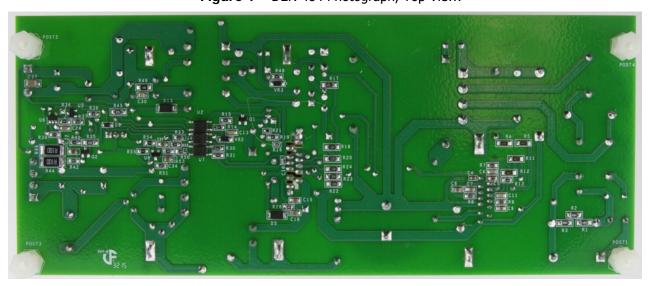


Figure 2 - DER-484 Photograph, Bottom View.

2 Power Supply Specification

The table below represents the specification for the design detailed in this report. Actual performance is listed in the results section. Detailed customer specification is shown below.

Description	Symbol	Min	Тур	Max	Units	Comment
Input Voltage Frequency	V _{IN} f _{LINE}	90 47	50/60	264 64	VAC Hz	2 Wire Input
Main Converter Output						
Output Voltage	Vo	0	61		V	61 VDC (nominal – otherwise defined by battery load).
Output Current	Io		4.59		Α	Nominal Current Limit Setting for Design.
Standby Converter Output						
Output Voltage	Vo	4.75	5.00	5.25	V	5 VDC ±5%
Output Current	I _o	0		4	Α	
Output Ripple (Optional)				50	mV P-P	20 MHz BW
Total Output Power Continuous Output Power Peak Output Power	Р _{оит} Р _{оит(РК)}		300	N/A	W	61 V / 4.59 A + 5 V / 4 A
Efficiency Total system at Full Load	η _{Main}	85	87.8	,	%	Measured at 115 VAC, Full Load
Environmental						
Conducted EMI		Meets CISPR22B / EN55022B			/ EN55022B	
Safety			Des	signed to I	meet IEC95	0 / UL1950 Class II
Ambient Temperature	T _{AMB}	0		60	°C	See Thermal Section for Conditions

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3 Schematic

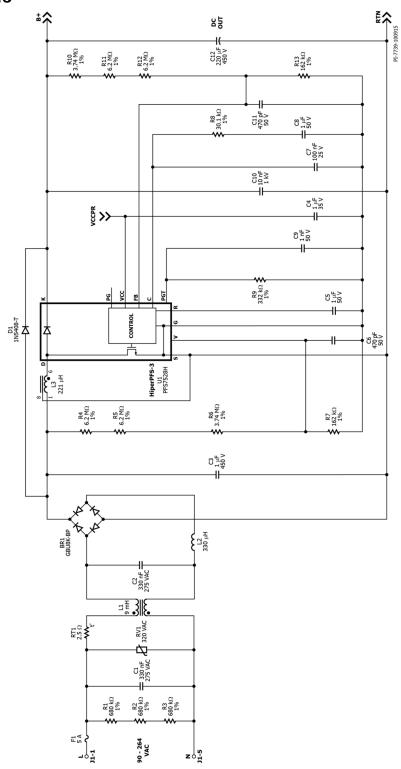


Figure 3 – Schematic Battery Charger Application Circuit - Input Filter, PFC Stage.

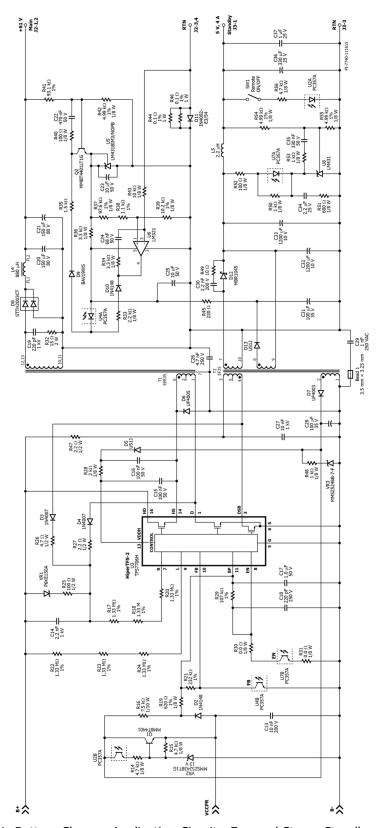


Figure 4 – Schematic Battery Charger Application Circuit - Forward Stage, Standby Supply, Bias Supplies and Output Voltage/Current Control.

P

4 Circuit Description

The schematic in Figures 3 and 4 shows a 2-switch forward power supply with flyback standby utilizing the TFS7706H, powered via a PFC front end utilizing the PFS7528H. The secondary control circuitry provides CV/CC control for use in battery charger applications

4.1 Input Filter / Boost Converter

The PFC input stage shown in Figure 3 is designed around the Power Integrations PFS7528H integrated PFC controller. This design provides a regulated output voltage of 385 VDC nominal, maintaining a high input power factor and overall efficiency over line and load, while remaining low in cost.

4.1.1 Input EMI Filter and Rectifier

Fuse F1 provides protection to the primary side circuitry and isolates it from the AC supply in the event of a fault. Diode bridge BR1 rectifies the AC input. Capacitors C1, C2, C26 and C29 in conjunction with inductors L1 and L2 constitute the EMI filter for attenuating both common mode and differential mode conducted noise. Film capacitor C3 provides input decoupling charge storage to reduce input ripple current at the switching frequencies and harmonics.

Resistors R1-R3 discharge the EMI filter capacitors after line voltage has been removed from the circuit.

Metal oxide varistor (MOV) RV1 protects the circuit during line surge events by effectively clamping the input voltage seen by the power supply.

4.1.2 PFS7528H Boost Converter

The boost converter stage consists of the boost inductor L3 and the PFS7528H IC (U1). This converter stage operates as a PFC boost converter, thereby maintaining a sinusoidal input current to the power supply while regulating the output DC voltage.

During start-up, diode D1 provides an inrush current path to the PFC output filter/bulk capacitor C12, bypassing the switching inductor L3 and switch U1 in order to prevent a resonant interaction between the switching inductor and output capacitor.

NTC thermistor RT1 limits inrush current of the supply when line voltage is first applied. Capacitor C10 provide a short, high-frequency return path to RTN for improved EMI results and to reduce U1 MOSFET drain voltage overshoot during turn-off. Capacitor C4 decouples and bypasses the U1 VCC pin. Capacitor C12 serves as output filter and energy storage for the PFC output.

Resistor R9 programs the output voltage level [via the POWER GOOD THRESHOLD (PGT) pin] below which the POWER GOOD (PG) pin will go into a high-impedance state.

Capacitor C5 on the REF pin of U1 is a noise decoupler for the internal reference and also programs the output power for either full mode, 100% of rated power [C10 = 1 μ F] or efficiency mode, 80% [C10 = 0.1 μ F] of rated power.

4.1.3 Input Feed Forward Sense Circuit

The input voltage of the power supply is sensed by the IC U1 using resistors R4-R7. Capacitor C6 bypasses the V pin on IC U1.

4.1.4 Output Feedback

Resistors R10-R13 constitute a voltage divider that provides a scaled voltage proportional to the output voltage as feedback to the controller IC U1, setting the PFC output voltage at 385 V. Capacitor C11 decouples the U1 FB pin.

Resistor R8 and capacitor C8 establish the control loop dominant pole, while C7 attenuates high-frequency noise.

4.2 Main Forward Converter / Standby

The schematic in Figure 4 depicts a 61 V, 280 W Forward DC-DC converter with constant voltage/ constant current output implemented using the TFS7706H.

Integrated circuit U3 incorporates the control circuitry, drivers and output MOSFETs necessary for a 2-switch forward converter and a flyback standby converter.

Components D3-4, C14, R25-27, and VR1 form a shared turn-off clamping circuit that limits the voltage at the U3 standby drain and establishes a higher-than-B+ reset voltage for T1 to allow a maximum duty cycle above 50%. Zener VR1 provides a defined clamp voltage and maintains a maximum voltage (150 V) on clamp capacitor C14 for higher light/no-load efficiency. The high side drain is clamped by D6.

Diode D5 provides biasing for the main converter high-side driver in U3, filtered and current limited by C15-16 and R28.

Most of the leakage and magnetizing energy associated with the main and standby converters is returned back to the B+ supply due to the slow recovery aspect of blocking diodes D3 and D4. During the main converter off-time, the main transformer is reset by a substantially higher voltage than $V_{\rm IN}$, hence the main converter can operate above 50% duty cycle, lowering RMS switch currents without penalizing holdup time.

The BYPASS (BP) pin along with C17 provides a decoupled regulated 5.85 V for the HiperTFS controller. The value for C17 (1 μ F) also selects the operating frequency of the main converter at 66 kHz. At start-up the bypass capacitor is charged from a current

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source internal to U3. When the BP pin voltage reaches 5.8 V, the standby converter can begin switching and both the secondary and primary-side bias voltages will begin to rise.

Output of the primary bias winding on T2 is used to supply power via resistors R16 and R19 to the HiperTFS BP pin during standby-only operation. Additional current is provided via a regulator consisting of Q1, R14-15, VR2, and C13 by the primary bias supply when remote-on switch SW1 activates U2A and U2B. The value of R19 is selected to satisfy the maximum current requirement of U3. The value of R16 is selected to maintain the minimum 700 μ A required into the BP pin to inhibit the internal HiperTFS high voltage current source and thus reduce no-load consumption.

The ENABLE (EN) pin is the feedback pin for the flyback standby controller section. Prior to start-up a resistor (R29) connected from EN to BP can be detected by the controller to select the internal current limit for standby section. The circuit presented here uses a $107~\rm k\Omega$ resistor (R29) at the EN pin to program a standby $I_{\rm LIM}$ of 750 mA (maximum). A capacitor (C18) is placed between EN and G to filter high frequency noise and help prevent pulse bunching, especially at maximum output power.

The FEEDBACK (FB) pin uses a 232 k Ω pull-up resistor (R21) to the BP pin, which selects the maximum primary current limit option for the U1 main forward converter. The FB pin provides feedback for the main converter. An increase in current sinking from FB pin to ground will reduce the operating duty cycle.

Capacitor C15 is the filtering and charge storage capacitor for the U1 high-side driver. During start-up the high-side MOSFET HS pin of U3 is briefly pulled to Source for 12 ms to precharge C5 using an internal current source. The nominal voltage on C5 during normal operation is internally shunt regulated to approximately 12 V. Components D5, C16, and R28 provide an efficient alternate source of current from the primary VCC supply, so that the internal high voltage supply for the high-side driver is turned off. This increases efficiency at light load and prevents main converter from pulse skipping, especially at light output loads.

Resistors R17-18 and R20 are used to translate the maximum available OFF time reset voltage into a current for the R pin and compare with the L pin current to compute the maximum allowable duty cycle to prevent saturation and to also determine the maximum allowable duty factor as a function of peak on-time flux.

The LINE-SENSE (L) pin provides an input bulk voltage line-sense function. This information is used by the undervoltage and overvoltage detection circuits for both the Main and standby sections. This pin can also be pulled down to Source to implement a remote-ON/OFF for both the standby and main supplies simultaneously. Resistors R22-R24 are used to translate the input voltage into a current for the L pin.

Components R56, SW1, and U2 (on the standby converter secondary output) provide remote start. When SW1 is closed, the output transistor of U2 turns on regulator O1 on the primary side of the supply, providing operating current to the main converter via the BP pin of U3. Opening SW1 turns off U2, shutting down the main converter function of U3, as well as U1.

4.3 Primary Bias Supply

The standby supply utilizes built-in capability of the U3 TFS2 device. Components D7 and C28 provide a 15 V (nominal) flyback bias supply for U1 and U3, generated from a primary-referred winding on standby transformer T2. Components R48 and VR3 clamp the primary VCC output voltage when the 5V standby supply is heavily loaded.

4.4 Main Output Rectification

The output of transformer T1 is rectified and filtered by D8, L4, and C20-21. Output rectifier D8 is a 300V ultrafast rectifier chosen for high efficiency. A snubber consisting of R32 and C19 helps limit the peak voltage excursion on the output rectifier.

4.5 Output Current and Voltage Control

Output current is sensed via resistors R44-45. These resistors are clamped by diode D11 to avoid damage to the current control circuitry during an output short circuit. Components R36 and U5 provide a voltage reference for current sense amplifier U6. Capacitor C25 stabilizes U6. The reference voltage for current sense amplifier U6 is divided down by R37-39. The default current limit setting is 4.589 A, as programmed by R44-45 and R37-39. Voltage from the current sense resistors is applied to the inverting input of U6 via R43. Opamp U6 drives optocoupler U4 through D10 and R33. Components R33-34, R43, and C24 are used for frequency compensation of the current loop.

Components Q2, R40-42, and C22 are used for output constant voltage control when the current limit is not engaged. Transistor Q2 drives optocoupler U4 via D9 and R35. Components R35, R40-42, and C22 affect the voltage control loop frequency compensation.

4.6 Standby Output

A 5 V, 4 A standby output is provided via a triple insulated winding on standby transformer T2. The standby 5 V output is available externally. The 5 V standby winding is rectified and filtered by D12, C32-33, and C36. Components L5 and C36 provide additional filtering to remove high frequency ripple and noise. Snubber C30 and R49 helps limit the peak voltage excursion on D12. The 5 V output is divided down by R54-55, and is applied to the reference input of error amplifier U8, which controls the standby section of U3 via R52 and U7. Resistor R50 provides bias current to U8, while C34 and R51 comprise a soft-finish network to eliminate output voltage overshoot at start-up. Components R52-53, and C35 compensate the standby control loop.

4.7 Secondary Bias Supply

Bias for the secondary control circuitry is supplied from a triple insulated winding on standby transformer T2. This winding is DC stacked on the 5 V standby output to improve regulation for the secondary bias supply. Otherwise, the bias voltage can vary considerably depending on the 5 V standby load, which can be any value form 0 A to 4 A. The standby supply is rectified and filtered by D13 and C31, with additional filtering by R45 and C25.

PCB Layout

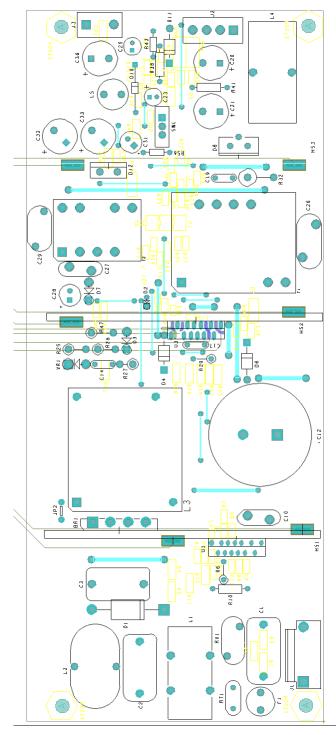


Figure 5 – Printed Circuit Layout, Showing Top Side Components with Bottom Side Traces.

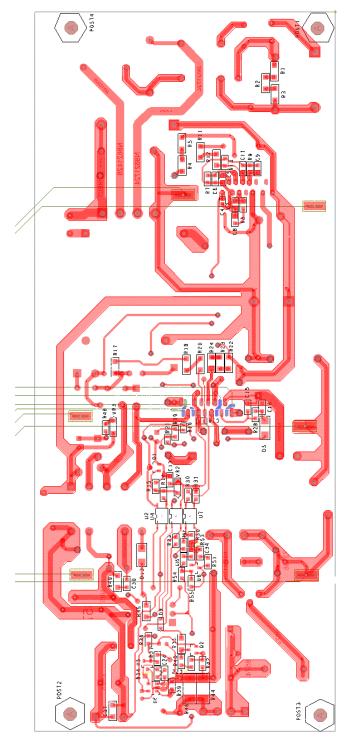


Figure 6 – Printed Circuit Layout, Bottom Side Traces and Components.

6 Bill of Materials

24	Item	Qty	Ref Des	Description	Mfg Part Number	Mfg
2	1	1	BEAD1		2643001501	Fair-Rite
3 2 C1 C2 330 nF, 275 VAC, Film, X2 ECQ-U2A334ML Panasonic	2	1	RD1		CRI IQV_RD	Micro Commercial
4 1 C3 1.0 μ, 450 V, METALPOLYPRO ECW-FZWLOSIA Panasonic, Tok 5 1 C4 1.μf 35 V, Ceramic, X7R, 0803 C1608X7RLV105M TDK 6 2 C5 C8 1.μf, 50 V, Ceramic, X7R, 0805 C2012X7R1H105M TDK 7 2 C6 C11 470 μf, 50 V, Ceramic, X7R, 0805 C08035C102KAT2A AVX 9 1 C9 1.nf, 50 V, Ceramic, X7R, 0805 08053C102KAT2A AVX 9 1 C9 1.nf, 50 V, Ceramic, X7R, 0805 08055C102KAT2A AVX 10 2 C10 C27 10 nf, 10 V, Disc Ceramic 56285HKM510 Vishay 11 1 C12 220 μf, 450 V, Electrolytic, Snap-In, (30 x 30) EKMQ45IVSN221M8305 United Chemi-cor 12 1 C11 C13 1.0 nf, 50 V, Ceramic, X7R, 0805 08055C103KATAA AVX 13 1 C14 2.2 nf, 1 kV, Ceramic, X7R, 0805 0805C103KATAA AVX 13 1 C14 2.2 nf, 10 V, Ceramic, X7R, 0805 C0080SKRDX7689BBH04 Ayapee	\vdash					
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7						
8 1 C7 100 Fr, 25 V, Ceramic, X7R, 0805 0805SC102KAT2A AVX 10 2 C10 C27 10 nF, 50 V, Ceramic, X7R, 0805 0805SC102KAT2A AVX 11 1 C12 220 μF, 450 V, Electrolytic, Snap-1n, (30 x 30) EKMQ51VSN22IMR305 Vishay 12 1 C12 220 μF, 450 V, Electrolytic, Snap-1n, (30 x 30) EKMQ51VSN22IMR305 Vishay 13 1 C14 2.2 nF, 1 kV, Ceramic, SN, 0.2" L.S. DEBB3A222KA2B Murata 14 2 C15 C16 100 nF, 50 V, Ceramic, X7R, 0805 CC080SKRX/R9B8104 Yageo 15 1 C17 1.0 μF, 50 V, Ceramic, X7R FR20X7RIH105K TDK 16 1 C18 220 pF, 250 V, Ceramic, X7R FR20X7RIH105K TDK 17 1 C19 1.0 μF, 50 V, Ceramic, X7R FR20X7RIH105K TDK 18 2 C2 C21 150 μF, 50 V, Ceramic, X7R, 0805 CC600SC622211 TDK 19 1 C12 2 470 nF, 50 V, Ceramic, X7R, 0805 GRN21gR71H374A888 Murata						
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20 2 C23 C25 10 μF, 50 V, Electrolytic, Gen. Purpose, (5 x 11) EKMG500ELL100ME11D Nippon Chemi-Cor 21 1 C24 68 nF, 50 V, Ceramic, X7R, 0805 C0805C683KSRACTU Kemet 22 1 C26 4.7 nF, Ceramic, Y1 440LD47-R Vishay 23 2 C28 C31 100 μF, 35 V, Electrolytic, Low ESR, 180 mΩ, (6.3 x 15) ELXZ350ELL10IMF15D Nippon Chemi-Cor 24 1 C29 1 nF, Ceramic, Y1 440LD10-R Vishay 25 1 C30 2.2 nF, 200 V, Ceramic, X7R, 0805 08052C222KAT2A AVX 26 2 C32 C33 1200 μF, 10 V, Electrolytic, Radial EEU-FMIA122 Panasonic 27 1 C34 2.2 μF, 25 V, Ceramic, X7R, 0805 C2012X7R1E225M TDK 28 1 C35 330 nF, 50 V, Ceramic, X7R, 0805 GRM219R71H334KA88 Murata 29 1 C36 330 uF, 25 V, Electrolytic, Low ESR, 90 mΩ, ELXZ250ELL331MJCSS Nippon Chemi-Cor 30 1 C37 1 μF, 25 V, Ceramic, X7R, 1206						
21 1 C24 68 nF, 50 V, Ceramic, X7R, 0805 C0805C683KSRACTU Kemet 22 1 C26 4.7 nF, Ceramic, Y1 440LD47-R Vishay 23 2 C28 C31 10 μF, 35 V, Electrolytic, Low ESR, 180 mΩ, (6.3 x 15) ELXZ350ELL101MF15D Nippon Chemi-Cord Mippon Chemi-Cord (6.3 x 15) 24 1 C29 1 nF, Ceramic, Y7R, 0805 08052C222KAT2A AVX 26 2 C32 C33 1200 μF, 10 V, Electrolytic, Radial EEU-FMIA122 Panasonic 27 1 C34 2.2 μF, 25 V, Ceramic, X7R, 0805 C2012X7R1E225M TDK 28 1 C35 330 nF, 50 V, Ceramic, X7R, 0805 GRM219R71H334KA88 Murata 29 1 C36 330 uF, 25 V, Electrolytic, Low ESR, 90 mΩ, (10 x 12.5) ELXZ250ELL331MJCSS Nippon Chemi-Cord (10 x 12.5) 30 1 C37 1 μF, 25 V, Ceramic, X7R, 1206 C3216X7R1E105K TDK 31 1 D1 1000 V, 3 A, Rectifier, DO-201AD 1N5408-T Diodes, Inc. 32 2 D2 D10 75 V, 300 mA, Fas						
22 1 C26 4.7 nF, Ceramic, Y1 440LD47-R Vishay 23 2 C28 C31 100 μF, 35 V, Electrolytic, Low ESR, 180 mΩ, (6.3 x 15) ELXZ350ELL101MF15D Nippon Chemi-Cord (6.3 x 15) 24 1 C29 1 nF, Ceramic, Y1 440LD10-R Vishay 25 1 C30 2.2 nF, 200 V, Ceramic, X7R, 0805 08052C222KAT2A AVX 26 2 C32 C33 1200 μF, 10 V, Electrolytic, Radial EEU-FM1A122 Panasonic 27 1 C34 2.2 μF, 25 V, Ceramic, X7R, 0805 C2012X7R1E225M TDK 28 1 C35 330 nF, 50 V, Ceramic, X7R, 0805 GRM219R71H334KA88 Murata 29 1 C36 330 uF, 25 V, Ceramic, X7R, 1206 C3216X7R1E105K TDK 30 1 C37 1 μF, 25 V, Ceramic, X7R, 1206 C3216X7R1E105K TDK 31 1 D1 1000 V, 3 A, Rectifier, DO-201AD 1N5408-T Diodes, Inc. 32 2 D2 D10 75 V, 300 mA, Fast Switching, DO-35 1N4148TR Vishay <td></td> <td></td> <td></td> <td></td> <td></td> <td></td>						
23 2 C28 C31 100 μF, 35 V, Electrolytic, Low ESR, 180 mΩ, (6.3 x 15) ELXZ350ELL101MF15D Nippon Chemi-Col (6.3 x 15) 24 1 C29 1 nF, Ceramic, Y1 440LD10-R Vishay 25 1 C30 2.2 nF, 200 V, Ceramic, X7R, 0805 08052C222KAT2A AVX 26 2 C32 C33 1200 μF, 10 V, Electrolytic, Radial EEU-FM1A122 Panasonic 27 1 C34 2.2 μF, 25 V, Ceramic, X7R, 0805 C2012X7R1E225M TDK 28 1 C35 330 nF, 50 V, Ceramic, X7R, 0805 GRM219R71H334KA88 Murata 29 1 C36 330 uF, 25 V, Electrolytic, Low ESR, 90 mΩ, (10 x 12.5) ELXZ250ELL331MJC5S Nippon Chemi-Col (10 x 12.5) 30 1 C37 1 μF, 25 V, Ceramic, X7R, 1206 C3216X7R1E105K TDK 31 1 D1 1000 V, 3 A, Rectifier, DO-201AD 1N5408-T Diodes, Inc. 31 1 D1 1000 V, 1 A, Rectifier, DO-201AD 1N4148TR Vishay 33 2 D2 D10 75 V, 300 mA, Fast Switching, DO-35<						
24 1 C29 1 nF, Ceramic, Y1 440LD10-R Vishay 25 1 C30 2.2 nF, 200 V, Ceramic, X7R, 0805 08052C22KAT2A AVX 26 2 C32 C33 1200 μF, 10 V, Electrolytic, Radial EEU-FMIA122 Panasonic 27 1 C34 2.2 μF, 25 V, Ceramic, X7R, 0805 C2012X7R1E225M TDK 28 1 C35 330 nF, 50 V, Ceramic, X7R, 0805 GRM219R71H334KA88 Murata 29 1 C36 330 uF, 25 V, Electrolytic, Low ESR, 90 mΩ, (10 x 12.5) ELXZ250ELL331MJC5S Nippon Chemi-Col (10 x 12.5) 30 1 C37 1 μF, 25 V, Ceramic, X7R, 1206 C3216X7R1E105K TDK 31 1 D1 1000 V, 3 A, Rectifier, DO-201AD 1N5408-T Diodes, Inc. 32 2 D2 D10 75 V, 300 mA, Fast Switching, DO-35 1N4148TR Vishay 34 2 D3 D4 1000 V, 1 A, Rectifier, DO-41 1N4007-E3/54 Vishay 35 1 D6 600 V, 1 A, Ultrafast Recovery, 75 ns, DO-41 UF4003-E3		1	C26		440LD47-K	Visitay
25 1 C30 2.2 nF, 200 V, Ceramic, X7R, 0805 08052C222KAT2A AVX 26 2 C32 C33 1200 μF, 10 V, Electrolytic, Radial EEU-FM1A122 Panasonic 27 1 C34 2.2 μF, 25 V, Ceramic, X7R, 0805 C2012X7R1E225M TDK 28 1 C35 330 nF, 50 V, Ceramic, X7R, 0805 GRM219R71H334KA88 Murata 29 1 C36 330 uF, 25 V, Electrolytic, Low ESR, 90 mΩ, (10 x 12.5) ELXZ250ELL331MJC5S Nippon Chemi-Cor 30 1 C37 1 μF, 25 V, Ceramic, X7R, 1206 C3216X7R1E105K TDK 31 1 D1 1000 V, 3 A, Rectifier, DO-201AD 1N5408-T Diodes, Inc. 32 2 D2 D10 75 V, 300 mA, Fast Switching, DO-35 1N4148TR Vishay 33 2 D3 D4 1000 V, 1 A, Rectifier, DO-41 1N4007-E3/54 Vishay 34 2 D5 D13 Diode Ultrafast, SW 600 V, 1 A, SMA US10-13-F Diodes, Inc. 35 1 D6 600 V, 1 A, Ultrafast Recovery, 75 ns, DO-41 UF4003-E3 </td <td>23</td> <td>2</td> <td>C28 C31</td> <td>(6.3 x 15)</td> <td>ELXZ350ELL101MF15D</td> <td>Nippon Chemi-Con</td>	23	2	C28 C31	(6.3 x 15)	ELXZ350ELL101MF15D	Nippon Chemi-Con
26 2 C32 C33 1200 μF, 10 V, Electrolytic, Radial EEU-FM1A122 Panasonic 27 1 C34 2.2 μF, 25 V, Ceramic, X7R, 0805 C2012X7R1E225M TDK 28 1 C35 330 nF, 50 V, Ceramic, X7R, 0805 GRM219R71H334KA88 Murata 29 1 C36 330 uF, 25 V, Electrolytic, Low ESR, 90 mΩ, (10 x 12.5) ELXZ250ELL331MJC5S Nippon Chemi-Col (10 x 12.5) 30 1 C37 1 μF, 25 V, Ceramic, X7R, 1206 C3216X7R1E105K TDK 31 1 D1 1000 V, 3 A, Rectifier, DO-201AD 1N5408-T Diodes, Inc. 32 2 D2 D10 75 V, 300 mA, Fast Switching, DO-35 1N4148TR Vishay 34 2 D5 D13 Diode Ultrafast, SW 600 V, 1 A, SMA US13-13-F Diodes, Inc. 35 1 D6 600 V, 1 A, Ultrafast Recovery, 75 ns, DO-41 UF4003-E3 Vishay 36 1 D7 200 V, 1 A, Diode ARRAY, GP, 35 ns, TO-220AB STTH2003CT ST Miscrs 38 1 D9 100 V, 0 A, Fast Switching, 50 ns, SOD-3						
C34 2.2 μF, 25 V, Ceramic, X7R, 0805 C2012X7R1E225M TDK						AVX
28 1 C35 330 nF, 50 V, Ceramic, X7R, 0805 GRM219R71H334KA88 Murata 29 1 C36 330 uF, 25 V, Electrolytic, Low ESR, 90 mΩ, (10 x 12.5) ELXZ250ELL331MJC5S Nippon Chemi-Cor 30 1 C37 1 μF, 25 V, Ceramic, X7R, 1206 C3216X7R1E105K TDK 31 1 D1 1000 V, 3 A, Rectifier, DO-201AD 1N5408-T Diodes, Inc. 32 2 D2 D10 75 V, 300 mA, Fast Switching, DO-35 1N4148TR Vishay 33 2 D3 D4 1000 V, 1 A, Rectifier, DO-41 1N4007-E3/54 Vishay 34 2 D5 D13 Diode Ultrafast, SW 600 V, 1 A, SMA US13-13-F Diodes, Inc. 35 1 D6 600 V, 1 A, Ultrafast Recovery, 75 ns, DO-41 UF4005-E3 Vishay 36 1 D7 200 V, 1 A, Ultrafast Recovery, 50 ns, DO-41 UF4005-E3 Vishay 37 1 D8 300 V, 10 A, Diode ARRAY, GP, 35 ns, TO-220AB STTH2003CT ST Miscrs 38 1 D9 100 V, 0.2 A, Fast Switching, 50 ns, SOD-323						
29 1 C36 330 uF, 25 V, Electrolytic, Low ESR, 90 mΩ, (10 x 12.5) ELXZ250ELL331MJCSS Nippon Chemi-Cor 30 1 C37 1 μF, 25 V, Ceramic, X7R, 1206 C3216X7R1E105K TDK 31 1 D1 1000 V, 3 A, Rectifier, DO-201AD 1N5408-T Diodes, Inc. 32 2 D2 D10 75 V, 300 mA, Fast Switching, DO-35 1N4148TR Vishay 33 2 D3 D4 1000 V, 1 A, Rectifier, DO-41 1N4007-E3/54 Vishay 34 2 D5 D13 Diode Ultrafast, SW 600 V, 1 A, SMA US11-13-F Diodes, Inc. 35 1 D6 600 V, 1 A, Ultrafast Recovery, 75 ns, DO-41 UF4005-E3 Vishay 36 1 D7 200 V, 1 A, Ultrafast Recovery, 50 ns, DO-41 UF4003-E3 Vishay 37 1 D8 300 V, 10 A, Diode ARRAY, GP, 35 ns, TO-220AB STTH2003CT ST Miscrs 38 1 D9 100 V, 0.2 A, Fast Switching, 50 ns, SOD-323 BAV19WS-7-F Diodes, Inc. 39 1 D11 100 V, 1 A, Rectifier, DO-41	$\overline{}$					
C36	28	1	C35		GRM219R71H334KA88	Murata
31 1 D1 1000 V, 3 A, Rectifier, DO-201AD 1N5408-T Diodes, Inc. 32 2 D2 D10 75 V, 300 mA, Fast Switching, DO-35 1N4148TR Vishay 33 2 D3 D4 1000 V, 1 A, Rectifier, DO-41 1N4007-E3/54 Vishay 34 2 D5 D13 Diode Ultrafast, SW 600 V, 1 A, SMA US1J-13-F Diodes, Inc. 35 1 D6 600 V, 1 A, Ultrafast Recovery, 75 ns, DO-41 UF4005-E3 Vishay 36 1 D7 200 V, 1 A, Ultrafast Recovery, 50 ns, DO-41 UF4003-E3 Vishay 37 1 D8 300 V, 10 A, Diode ARRAY, GP, 35 ns, TO-220AB STTH2003CT ST Miscrs 38 1 D9 100 V, 0.2 A, Fast Switching, 50 ns, SOD-323 BAV19WS-7-F Diodes, Inc. 39 1 D11 100 V, 1 A, Rectifier, DO-41 1N4002-E3/54 Vishay 40 1 D12 45 V, 10 A, Schottky, TO-220AC MBR1045 Vishay 41 2 ESIPCLIP M4 METAL1 ESIPCLIP M4 METAL1 ESIPCLIP M4 METAL2 Heat Sink Hardware, Edge Clip, 20.7	29	1	C36		ELXZ250ELL331MJC5S	Nippon Chemi-Con
32 2 D2 D10 75 V, 300 mA, Fast Switching, DO-35 1N4148TR Vishay 33 2 D3 D4 1000 V, 1 A, Rectifier, DO-41 1N4007-E3/54 Vishay 34 2 D5 D13 Diode Ultrafast, SW 600 V, 1 A, SMA US1J-13-F Diodes, Inc. 35 1 D6 600 V, 1 A, Ultrafast Recovery, 75 ns, DO-41 UF4005-E3 Vishay 36 1 D7 200 V, 1 A, Ultrafast Recovery, 50 ns, DO-41 UF4003-E3 Vishay 37 1 D8 300 V, 10 A, Diode ARRAY, GP, 35 ns, TO-220AB STTH2003CT ST Miscrs 38 1 D9 100 V, 0.2 A, Fast Switching, 50 ns, SOD-323 BAV19WS-7-F Diodes, Inc. 39 1 D11 100 V, 1 A, Rectifier, DO-41 1N4002-E3/54 Vishay 40 1 D12 45 V, 10 A, Schottky, TO-220AC MBR1045 Vishay 41 2 ESIPCLIP M4 METAL1 METAL2 Heat Sink Hardware, Edge Clip, 20.76 mm L x 8 mm W x 0.015 mm Thk NP975864 Aavid Thermalloy 42 1 F1 5 A, 250 V, Slow, TR5	30	1	C37	1 μF, 25 V, Ceramic, X7R, 1206	C3216X7R1E105K	TDK
33 2 D3 D4 1000 V, 1 A, Rectifier, DO-41 1N4007-E3/54 Vishay 34 2 D5 D13 Diode Ultrafast, SW 600 V, 1 A, SMA US13-13-F Diodes, Inc. 35 1 D6 600 V, 1 A, Ultrafast Recovery, 75 ns, DO-41 UF4005-E3 Vishay 36 1 D7 200 V, 1 A, Ultrafast Recovery, 50 ns, DO-41 UF4003-E3 Vishay 37 1 D8 300 V, 10 A, Diode ARRAY, GP, 35 ns, TO-220AB STTH2003CT ST Miscrs 38 1 D9 100 V, 0.2 A, Fast Switching, 50 ns, SOD-323 BAV19WS-7-F Diodes, Inc. 39 1 D11 100 V, 1 A, Rectifier, DO-41 1N4002-E3/54 Vishay 40 1 D12 45 V, 10 A, Schottky, TO-220AC MBR1045 Vishay 41 2 ESIPCLIP M4 METAL2 Heat Sink Hardware, Edge Clip, 20.76 mm L x 8 mm W x 0.015 mm Thk NP975864 Aavid Thermalloy 42 1 F1 5 A, 250 V, Slow, TR5 37215000411 Wickman 43 1 HOTMELT_V? Adhesive, Hot Melt, VO 37	31	1	D1	1000 V, 3 A, Rectifier, DO-201AD	1N5408-T	Diodes, Inc.
34 2 D5 D13 Diode Ultrafast, SW 600 V, 1 A, SMA US1J-13-F Diodes, Inc. 35 1 D6 600 V, 1 A, Ultrafast Recovery, 75 ns, DO-41 UF4005-E3 Vishay 36 1 D7 200 V, 1 A, Ultrafast Recovery, 50 ns, DO-41 UF4003-E3 Vishay 37 1 D8 300 V, 10 A, Diode ARRAY, GP, 35 ns, TO-220AB STTH2003CT ST Miscrs 38 1 D9 100 V, 0.2 A, Fast Switching, 50 ns, SOD-323 BAV19WS-7-F Diodes, Inc. 39 1 D11 100 V, 1 A, Rectifier, DO-41 1N4002-E3/54 Vishay 40 1 D12 45 V, 10 A, Schottky, TO-220AC MBR1045 Vishay 41 2 METAL1 ESIPCLIP M4 METAL2 Heat Sink Hardware, Edge Clip, 20.76 mm L x 8 mm W x 0.015 mm Thk NP975864 Aavid Thermalloy 42 1 F1 5 A, 250 V, Slow, TR5 37215000411 Wickman 43 1 HOTMELT_V? Adhesive, Hot Melt, VO 3748 VO-TC 3M 44 1 HS1 FAB, Heat Sink, PFS Bridge, DER484 <t< td=""><td>32</td><td>2</td><td>D2 D10</td><td>75 V, 300 mA, Fast Switching, DO-35</td><td>1N4148TR</td><td>Vishay</td></t<>	32	2	D2 D10	75 V, 300 mA, Fast Switching, DO-35	1N4148TR	Vishay
35 1 D6 600 V, 1 A, Ultrafast Recovery, 75 ns, DO-41 UF4005-E3 Vishay 36 1 D7 200 V, 1 A, Ultrafast Recovery, 50 ns, DO-41 UF4003-E3 Vishay 37 1 D8 300 V, 10 A, Diode ARRAY, GP, 35 ns, TO-220AB STTH2003CT ST Miscrs 38 1 D9 100 V, 0.2 A, Fast Switching, 50 ns, SOD-323 BAV19WS-7-F Diodes, Inc. 39 1 D11 100 V, 1 A, Rectifier, DO-41 1N4002-E3/54 Vishay 40 1 D12 45 V, 10 A, Schottky, TO-220AC MBR1045 Vishay 41 2 METAL1 ESIPCLIP M4 METAL2 Heat Sink Hardware, Edge Clip, 20.76 mm L x 8 mm W x 0.015 mm Thk NP975864 Aavid Thermalloy 42 1 F1 5 A, 250 V, Slow, TR5 37215000411 Wickman 43 1 HOTMELT_V? Adhesive, Hot Melt, VO 3748 VO-TC 3M 44 1 HS1 FAB, Heat Sink, PFS eSIP, DER484 Custom 45 1 HS2 FAB, Heat Sink, PFS Diode, DER484 Custom	33	2	D3 D4	1000 V, 1 A, Rectifier, DO-41		Vishay
36 1 D7 200 V, 1 A, Ultrafast Recovery, 50 ns, DO-41 UF4003-E3 Vishay 37 1 D8 300 V, 10 A, Diode ARRAY, GP, 35 ns, TO-220AB STTH2003CT ST Miscrs 38 1 D9 100 V, 0.2 A, Fast Switching, 50 ns, SOD-323 BAV19WS-7-F Diodes, Inc. 39 1 D11 100 V, 1 A, Rectifier, DO-41 1N4002-E3/54 Vishay 40 1 D12 45 V, 10 A, Schottky, TO-220AC MBR1045 Vishay 41 2 ESIPCLIP M4 METAL1 ESIPCLIP M4 METAL2 Heat Sink Hardware, Edge Clip, 20.76 mm L x 8 mm W x 0.015 mm Thk NP975864 Aavid Thermalloy 42 1 F1 5 A, 250 V, Slow, TR5 37215000411 Wickman 43 1 HOTMELT_V? Adhesive, Hot Melt, VO 3748 VO-TC 3M 44 1 HS1 FAB, Heat Sink, PFS Bridge, DER484 Custom 45 1 HS2 FAB, Heat Sink, PFS Diode, DER484 Custom 46 1 HS3 FAB, Heat Sink, PFS Diode, DER484 Custom	34	2	D5 D13	Diode Ultrafast, SW 600 V, 1 A, SMA	US1J-13-F	Diodes, Inc.
37 1 D8 300 V, 10 A, Diode ARRAY, GP, 35 ns, TO-220AB STTH2003CT ST Miscrs 38 1 D9 100 V, 0.2 A, Fast Switching, 50 ns, SOD-323 BAV19WS-7-F Diodes, Inc. 39 1 D11 100 V, 1 A, Rectifier, DO-41 1N4002-E3/54 Vishay 40 1 D12 45 V, 10 A, Schottky, TO-220AC MBR1045 Vishay 41 2 ESIPCLIP M4 METAL1 ESIPCLIP M4 METAL2 Heat Sink Hardware, Edge Clip, 20.76 mm L x 8 mm W x 0.015 mm Thk NP975864 Aavid Thermalloy 42 1 F1 5 A, 250 V, Slow, TR5 37215000411 Wickman 43 1 HOTMELT_V? Adhesive, Hot Melt, VO 3748 VO-TC 3M 44 1 HS1 FAB, Heat Sink, PFS Bridge, DER484 Custom 45 1 HS2 FAB, Heat Sink, PFS eSIP, DER484 Custom 46 1 HS3 FAB, Heat Sink, PFS Diode, DER484 Custom	35	1	D6	600 V, 1 A, Ultrafast Recovery, 75 ns, DO-41	UF4005-E3	Vishay
38 1 D9 100 V, 0.2 A, Fast Switching, 50 ns, SOD-323 BAV19WS-7-F Diodes, Inc. 39 1 D11 100 V, 1 A, Rectifier, DO-41 1N4002-E3/54 Vishay 40 1 D12 45 V, 10 A, Schottky, TO-220AC MBR1045 Vishay 41 2 ESIPCLIP M4 METAL1 ESIPCLIP M4 METAL2 Heat Sink Hardware, Edge Clip, 20.76 mm L x 8 mm W x 0.015 mm Thk NP975864 Aavid Thermalloy 42 1 F1 5 A, 250 V, Slow, TR5 37215000411 Wickman 43 1 HOTMELT_V? Adhesive, Hot Melt, VO 3748 VO-TC 3M 44 1 HS1 FAB, Heat Sink, PFS Bridge, DER484 Custom 45 1 HS2 FAB, Heat Sink, PFS eSIP, DER484 Custom 46 1 HS3 FAB, Heat Sink, PFS Diode, DER484 Custom	36	1	D7	200 V, 1 A, Ultrafast Recovery, 50 ns, DO-41	UF4003-E3	Vishay
39 1 D11 100 V, 1 A, Rectifier, DO-41 1N4002-E3/54 Vishay 40 1 D12 45 V, 10 A, Schottky, TO-220AC MBR1045 Vishay 41 2 ESIPCLIP M4 METAL1 ESIPCLIP M4 METAL2 Heat Sink Hardware, Edge Clip, 20.76 mm L x 8 mm W x 0.015 mm Thk NP975864 Aavid Thermalloy 42 1 F1 5 A, 250 V, Slow, TR5 37215000411 Wickman 43 1 HOTMELT_V? Adhesive, Hot Melt, VO 3748 VO-TC 3M 44 1 HS1 FAB, Heat Sink, PFS Bridge, DER484 Custom 45 1 HS2 FAB, Heat Sink, PFS eSIP, DER484 Custom 46 1 HS3 FAB, Heat Sink, PFS Diode, DER484 Custom	37	1	D8	300 V, 10 A, Diode ARRAY, GP, 35 ns, TO-220AB	STTH2003CT	ST Miscrs
40 1 D12 45 V, 10 A, Schottky, TO-220AC MBR1045 Vishay 41 2 ESIPCLIP M4 METAL1 ESIPCLIP M4 METAL2 Heat Sink Hardware, Edge Clip, 20.76 mm L x 8 mm W x 0.015 mm Thk NP975864 Aavid Thermalloy 42 1 F1 5 A, 250 V, Slow, TR5 37215000411 Wickman 43 1 HOTMELT_V? Adhesive, Hot Melt, VO 3748 VO-TC 3M 44 1 HS1 FAB, Heat Sink, PFS Bridge, DER484 Custom 45 1 HS2 FAB, Heat Sink, PFS eSIP, DER484 Custom 46 1 HS3 FAB, Heat Sink, PFS Diode, DER484 Custom		1		100 V, 0.2 A, Fast Switching, 50 ns, SOD-323	BAV19WS-7-F	Diodes, Inc.
ESIPCLIP M4 Heat Sink Hardware, Edge Clip, 20.76 mm L x 8 mm NP975864 Aavid Thermalloy	39	1			1N4002-E3/54	Vishay
41 2 METAL1 ESIPCLIP M4 METAL2 Heat Sink Hardware, Edge Clip, 20.76 mm L x 8 mm W x 0.015 mm Thk NP975864 Aavid Thermalloy 42 1 F1 5 A, 250 V, Slow, TR5 37215000411 Wickman 43 1 HOTMELT_V? Adhesive, Hot Melt, VO 3748 VO-TC 3M 44 1 HS1 FAB, Heat Sink, PFS Bridge, DER484 Custom 45 1 HS2 FAB, Heat Sink, PFS eSIP, DER484 Custom 46 1 HS3 FAB, Heat Sink, PFS Diode, DER484 Custom	40	1		45 V, 10 A, Schottky, TO-220AC	MBR1045	Vishay
41 2 ESIPCLIP M4 METAL2 W x 0.015 mm Thk NP9/3864 Advid Thermalicy 42 1 F1 5 A, 250 V, Slow, TR5 37215000411 Wickman 43 1 HOTMELT_V? Adhesive, Hot Melt, VO 3748 VO-TC 3M 44 1 HS1 FAB, Heat Sink, PFS Bridge, DER484 Custom 45 1 HS2 FAB, Heat Sink, PFS eSIP, DER484 Custom 46 1 HS3 FAB, Heat Sink, PFS Diode, DER484 Custom						
42 1 F1 5 A, 250 V, Slow, TR5 37215000411 Wickman 43 1 HOTMELT_V? Adhesive, Hot Melt, VO 3748 VO-TC 3M 44 1 HS1 FAB, Heat Sink, PFS Bridge, DER484 Custom 45 1 HS2 FAB, Heat Sink, PFS eSIP, DER484 Custom 46 1 HS3 FAB, Heat Sink, PFS Diode, DER484 Custom	41	2	ESIPCLIP M4		NP975864	Aavid Thermalloy
43 1 HOTMELT_V? Adhesive, Hot Melt, VO 3748 VO-TC 3M 44 1 HS1 FAB, Heat Sink, PFS Bridge, DER484 Custom 45 1 HS2 FAB, Heat Sink, PFS eSIP, DER484 Custom 46 1 HS3 FAB, Heat Sink, PFS Diode, DER484 Custom	42	1		5 A, 250 V, Slow, TR5	37215000411	Wickman
44 1 HS1 FAB, Heat Sink, PFS Bridge, DER484 Custom 45 1 HS2 FAB, Heat Sink, PFS eSIP, DER484 Custom 46 1 HS3 FAB, Heat Sink, PFS Diode, DER484 Custom						
45 1 HS2 FAB, Heat Sink, PFS eSIP, DER484 Custom 46 1 HS3 FAB, Heat Sink, PFS Diode, DER484 Custom				, ,	-	
46 1 HS3 FAB, Heat Sink, PFS Diode, DER484 Custom						
THE TEMPORAL PROBLEM (LEAD) DEGLET, U.150 DILCTI, VERLICAL L. UUZ00U4U5U L. MOIEX	47	1	J1	5 Position (1 x 5) header, 0.156 pitch, Vertical	0026604050	Molex



48	1	J2	4 Position (1 x 4) header, 0.156 pitch, Vertical	26-48-1045	Molex
49	1	J3	3 Position (1 x 3) header, 0.156 pitch, Vertical	26-48-1031	Molex
50	2	JP1 JP14	Wire Jumper, Insulated, TFE, #18 AWG, 0.9 in	C2052A-12-02	Alpha
51	1	JP2	Wire Jumper, Non insulated, #22 AWG, 0.2 in	298	Alpha
52	3	JP3 JP19 JP24	Wire Jumper, Insulated, TFE, #18 AWG, 0.8 in	C2052A-12-02	Alpha
53	1	JP4	Wire Jumper, Insulated, #24 AWG, 0.6 in	C2003A-12-02	Gen Cable
54	1	JP5	Wire Jumper, Non insulated, #22 AWG, 1.0 in	298	Alpha
55	2	JP6 JP22	Wire Jumper, Insulated, #24 AWG, 0.3 in	C2003A-12-02	Gen Cable
56	2	JP7 JP17	Wire Jumper, Insulated, #24 AWG, 0.8 in	C2003A-12-02	Gen Cable
57	2	JP8 JP15	Wire Jumper, Insulated, TFE, #18 AWG, 0.6 in	C2052A-12-02	Alpha
58	1	JP9	Wire Jumper, Insulated, #24 AWG, 0.7 in	C2003A-12-02	Gen Cable
59	1	JP10	Wire Jumper, Non insulated, #22 AWG, 0.5 in	298	Alpha
60	1	JP11	Wire Jumper, Non insulated, #22 AWG, 0.4 in	298	Alpha
61	1	JP12	Wire Jumper, Insulated, TFE, #18 AWG, 0.3 in	C2052A-12-02	Alpha
62	1	JP13	Wire Jumper, Insulated, TFE, #18 AWG, 0.4 in	C2052A-12-02	Alpha
63	1	JP16	Wire Jumper, Non Insulated, #18 AWG, 0.1 in	296 SV001	Alpha
64	1	JP18	Wire Jumper, Insulated, #24 AWG, 0.5 in	C2003A-12-02	Gen Cable
65	2	JP20 JP23	Wire Jumper, Non insulated, #22 AWG, 0.3 in	298	Alpha
66	1	JP21	Wire Jumper, Insulated, #24 AWG, 1.0 in	C2003A-12-02	Gen Cable
- 00	1	JF21		T22148-902S P.I.	
67	1	L1	9 mH, 5 A, Common Mode Choke	Custom	Fontaine
68	1	L2	330 μH, 3.3 A, Vertical Toroidal	2218-V-RC VTK-00037	Bourns Premier Magnetics
69	1	L3	Custom, PFC Inductor, 221 μH, PQ32/20, Vertical	BQ32/30-1112CPFR TSD-4013	TDK Premier Magnetics
70	1	L4	Custom, 880 μH, Constructed on core AllStar T28*12*14 from PI #32-00308-00	TSD-4014	Premier Magnetics
71	1	L5	2.2 uH, 6.0 A	RFB0807-2R2L TSD-4015	Coilcraft Premier Magnetics
72	4	POST1 POST2 POST3 POST4	Post, Circuit Board, Female, Hex, 6-32, snap, 0.375L, Nylon	561-0375A	Eagle Hardware
73	2	Q1 Q2	NPN, Small Signal BJT, GP SS, 40 V, 0.6 A, SOT-23	MMBT4401LT1G	Diodes, Inc.
74	3	R1 R2 R3	680 kΩ, 5%, 1/4 W, Thick Film, 1206	ERJ-8GEYJ684V	Panasonic
75	4	R4 R5 R11 R12	6.2 MΩ, 1%, 1/4 W, Thick Film, 1206	KTR18EZPF6204	Rohm Semi
76	2	R6 R10	3.74 MΩ, 1%, 1/4 W, Metal Film	MFR-25FBF52-3M74	Yageo
77	2	R7 R13	162 kΩ, 1%, 1/8 W, Thick Film, 0805	ERJ-6ENF1623V	Panasonic
78	1	R8	30.1 kΩ, 1%, 1/8 W, Thick Film, 0805	ERJ-6ENF3012V	Panasonic
79	1	R9	332 kΩ, 1%, 1/8 W, Thick Film, 0805	ERJ-6ENF3323V	Panasonic
80	2	R14 R15	4.7 kΩ, 5%, 1/8 W, Thick Film, 0805	ERJ-6GEYJ472V	Panasonic
81	1	R16	7.5 kΩ, 5%, 1/10 W, Thick Film, 0603	ERJ-3GEYJ752V	Panasonic
82	6	R17 R18 R20 R22 R23 R24	1.33 MΩ, 1%, 1/4 W, Thick Film, 1206	RC1206FR-071M33L	Yageo
83	1	R19	620Ω, 5%, 1/8 W, Thick Film, 0805	ERJ-6GEYJ621V	Panasonic
84	1	R21	232 kΩ, 1%, 1/16 W, Thick Film, 0603	ERJ-3EKF2323V	Panasonic
85	1	R25	100Ω , 5%, 1/2 W, Carbon Film	CF12JT100R	Stackpole
86	1	R26	4.7 Ω, 5%, 1/2 W, Carbon Film	CFR-50JB-4R7	Yageo
87	1	R27	2.2 Ω, 5%, 1/2 W, Carbon Film	CFR-50JB-2R2	Yageo
88	1	R28	2 kΩ, 5%, 1/8 W, Thick Film, 0805	ERJ-6GEYJ202V	Panasonic
89	1	R29	107 kΩ, 1%, 1/4 W, Metal Film	MFR-25FBF-107K	Yageo
90	2	R30 R31	0 Ω 5%, 1/8 W, Thick Film, 0805	ERJ-6GEY0R00V	Panasonic
91	1	R32	15 Ω, 5%, 2 W, Metal Oxide	RSF200JB-15R	Yageo
92	1	R33	2.2 kΩ, 5%, 1/8 W, Thick Film, 0805	ERJ-6GEYJ222V	Panasonic
93	2	R34 R36	3.3 kΩ, 5%, 1/8 W, Thick Film, 0805	ERJ-6GEYJ332V	Panasonic
94	1	R35	1.5 kΩ, 5%, 1/4 W, Thick Film, 1206	ERJ-8GEYJ152V	Panasonic
95	1	R37	97.6 kΩ, 1%, 1/8 W, Thick Film, 0805	ERJ-6ENF9762V	Panasonic
93	1	V)/	37.0 K22, 170, 1/0 W, THICK FIIII, UOU3	LICU-ULINES/UZV	r ai iaSUI IIC



96	1	R38	1.1 kΩ, 1%, 1/4 W, Metal Film	MFR-25FBF-1K10	Yageo
97	1	R39	10.2 kΩ, 1%, 1/8 W, Thick Film, 0805	ERJ-6ENF1022V	Panasonic
98	2	R40 R52	100 Ω, 5%, 1/8 W, Thick Film, 0805	ERJ-6GEYJ101V	Panasonic
99	1	R41	93.1 kΩ, 1%, 1/4 W, Metal Film	MFR-25FBF-93K1	Yageo
100	3	R42 R54 R55	4.99 kΩ, 1%, 1/8 W, Thick Film, 0805	ERJ-6ENF4991V	Panasonic
101	1	R43	10 kΩ, 5%, 1/8 W, Carbon Film	CF18JT10K0	Stackpole
102	2	R44 R46	0.1 Ω, 1%, 1 W, Thick Film, 2512	RL2512FK-070R1L	Yageo
103	1	R45	220 Ω, 5%, 1/4 W, Thick Film, 1206	ERJ-8GEYJ221V	Panasonic
104	1	R47	2.2 Ω, 5%, 1/2 W, Metal Film, Fusible/Flame Proof	NFR25H0002208JR500	Vishay
105	3	R48 R50 R53	1 kΩ, 5%, 1/8 W, Thick Film, 0805	ERJ-6GEYJ102V	Panasonic
106	1	R49	10 Ω, 5%, 1/4 W, Thick Film, 1206	ERJ-8GEYJ100V	Panasonic
107	1	R51	680 Ω, 5%, 1/8 W, Thick Film, 0805	ERJ-6GEYJ681V	Panasonic
108	1	R56	4.7 kΩ, 5%, 1/8 W, Carbon Film	CF18JT4K70	Stackpole
109	1	RT1	NTC Thermistor, 2.5 Ohms, 5 A	SL10 2R505	Ametherm
110	3	RTV1 RTV2 RTV3	Thermally conductive Silicone Grease	120-SA	Wakefield
111	1	RV1	320 V, 23 J, 10 mm, RADIAL	V320LA10P	Littlefuse
112	3	SCREW1 SCREW3 SCREW4	SCREW MACHINE PHIL 4-40 X 1/4 SS	PMSSS 440 0025 PH	Building Fasteners
113	2	SCREW2 SCREW5	SCREW MACHINE PHIL 4-40X 3/16 SS	67413609	MSC Industrial
114	2	SPACER_CER1 SPACER_CER2	SPACER RND, Steatite C220 Ceramic	CER-2	Richco
115	1	SW1	SWITCH SLIDE SPDT 30 V, .2 A PC MNT	EG1218	E-Switch
116	1	T1	Transformer, EER35, Vertical, 14 Custom	TSD-4016	Premier Magnetics
117	1	T2	Transformer, EF25/13/7, Vertical, Custom	TSD-4017	Premier Magnetics
118	2	TO-220 PAD1 TO-220 PAD2	THERMAL PAD TO-220 .009" SP1000	1009-58	Bergquist
119	1	U1	HiperPFS-3, eSIP16/13	PFS7528H	Power Integrations
120	3	U2 U4 U7	Optocoupler, 80 V, CTR 80-160%, 4-Mini Flat	PC357N1TJ00F	Sharp
121	1	U3	HiperTFS-2, ESIP16/12	TFS7706H	Power Integrations
122	1	U5	IC, REG ZENER SHUNT ADJ SOT-23	LM431BIM3/NOPB	National Semi
123	1	U6	OP AMP SINGLE LOW PWR SOT23-5	LM321MF	National Semi
124	1	U8	IC, REG ZENER SHUNT ADJ SOT-23	LM431AIM3/NOPB	National Semi
125	1	VR1	150 V, 5 W, 5%, TVS, DO204AC (DO-15)	P6KE150A	LittleFuse
126	1	VR2	13 V, 5%, 500 mW, SOD-123	MMSZ5243BT1G	ON Semi
127	1	VR3	Diode Zener 18 V 500 MW SOD123	MMSZ5248B-7-F	Diodes, Inc.
128	1	WASHER1	WASHER FLAT #4 SS	FWSS 004	Building Fasteners
129	4	WASHER2 WASHER3 WASHER4 WASHER5	WASHER FLAT #4 Zinc, OD 0.219, ID 0.125, Thk 0.032, Yellow Chromate Finish	5205820-2	Тусо
130	2	WASHER6 WASHER7	Washer, Shoulder, #4, 0.032 Shoulder x 0.116" Dia, Polyphenylene Sulfide PPS	7721-7PPSG	Aavid Thermalloy



7 Magnetics

7.1 PFC Boost Inductor (L3) Specification

7.1.1 Electrical Diagram

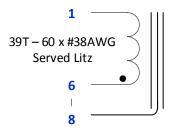


Figure 7 – PFC Inductor Schematic Diagram.

7.1.2 Electrical Specification

Inductance	Pins 1-6, measured at 100 kHz, 0.4 V _{RMS} .	221 μH ±5%
Resonant Frequency	Pins 1-6.	1300 kHz (Min.)

7.1.3 Material List

Item	Description
[1]	Core: TDK-PC44PQ32/30Z or equivalent, gapped for A _{LG} of 145 nH/T ² .
[2]	Bobbin: PQ32/30, Phenolic, Vertical, 12 pins (6/6). TDK BPQ32/30-112CPFR or equivalent.
[3]	Magnet wire: Served Litz wire 60 x #38 AWG, Single Coated Solderable.
[4]	Tape: Polyester Film, 3M 1350F-1 or equivalent, 17.6 mm wide.
[5]	Tape: Polyester Film, 3M 1350F-1 or equivalent, 13 mm wide.
[6]	Tinned Bus Wire: #24 AWG.
[7]	Varnish: Dolph BC-359 or equivalent.

7.1.4 Build Diagram

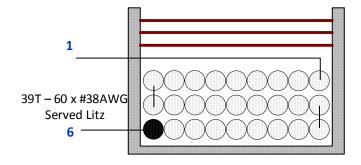


Figure 8 – PFC Inductor Build Diagram.

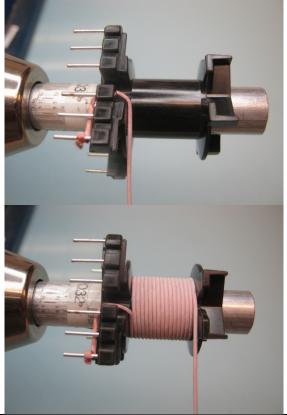
7.1.5 Winding Illustrations

Winding Preparation



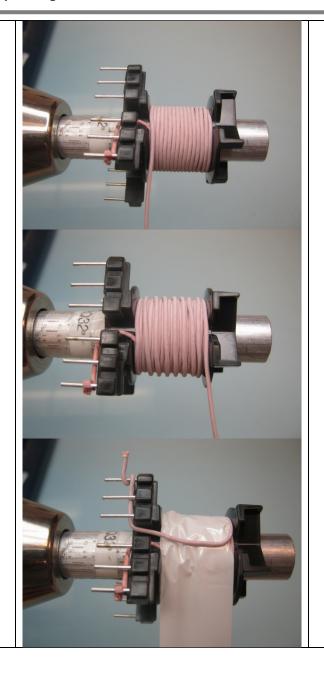
Place the bobbin item [2] on the mandrel with the pin side is on the left side. Winding direction is clockwise direction.

Winding



Start at pin 6, wind 39 turns of wire item [3] in 2 1/2 layers, spread wire evenly on last layer, and finish at pin 1. Route start and finish leads on bobbin bottom as shown in pictures.

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Place 3 layers of tape item Insulation Grind core to get specified inductance. Assemble core halves in bobbin. Attach bus wire item [6] to pin 8 of bobbin [2].Bend as shown in pictures. Position wire in in center of **Final Assembly** core as shown. Secure wire and core halves with three layers of tape [5], trapping wire [6] against core halves. Remove pins: 2, 3, 4, 5, 7, 9, 10, 11. Varnish item [7].

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7.2 Main Transformer (T1) Specification

7.2.1 Electrical Diagram

Figure 9 – Main Forward Transformer Schematic.

7.2.2 Electrical Specifications

Electrical Strength	1 second, 60 Hz, from pins 1-6 to 10-13.	3000 VAC
Primary Inductance	Pins 1-6 all other windings open, measured at 100 kHz, 0.4 V_{RMS} .	23 mH ±20%
Resonant Frequency	Pins 1-6, all other windings open.	150 kHz (Min.)
Primary Leakage Inductance	Pins 1-6, with pins 10-13 shorted, measured at 100 kHz, 0.4 V_{RMS} .	10 μH (Max.)

7.2.3 Material List

Item	Description
[1]	Core Pair EER35: TDK PC95 or equivalent.
[2]	Bobbin: EER35 Vertical, 14 pins, PI Part # 25-00029-00, Ying Chin YC-3508 or equivalent.
[3]	Wire, Triple Insulated, #23 AWG – Furukawa Tex-E or equivalent.
[4]	Wire, Magnet, Solderable Double Coated, #25 AWG.
[5]	Tape: Polyester Film, 3M 1350F-1 or equivalent, 26 mm wide.
[6]	Tape: Polyester Web, 3M 44 or equivalent, 3 mm wide.
[7]	Tape: Copper Foil, 3M 1194 or equivalent, 13 mm wide.
[8]	Transformer Varnish: Dolph BC-359, or equivalent.

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7.2.4 Build Diagram

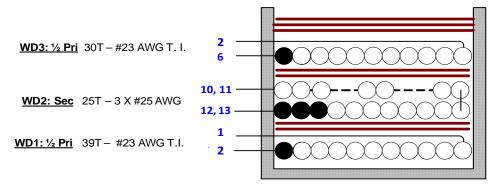


Figure 10 – Transformer Build Diagram.

7.2.5 Winding Instructions

General Note	For the purpose of these instructions, bobbin is oriented on winder such that pins are on the left side (see illustration). Winding direction as shown is clockwise.
WD1: ½ Primary	Starting on pin 2, wind 30 turns of triple insulated wire item [3] in 1 layer, Wind remaining 9 turns back evenly across bobbin window, finish on pin 1.
Insulation	Apply 2 layers of tape item [5].
Margin	Using tape item [6], apply a 3mm margin to pins side of bobbin. Match height of WD2.
WD2: Secondary	Starting at pins 12 & 13, wind 25 trifilar turns of wire item [4] in 2 layers, finishing at pins 10 and 11.
Insulation	Apply 2 layers of tape item [5].
WD3: ½ Primary	Starting on pin 6, wind 30 turns of triple insulated wire item [3] in 1 layer, and finish on pin 2.
Insulation	Apply 3 layers of tape item [5].
Assembly (1)	Assemble gapped core halves in bobbin, secure with tape. Using copper tape item [7], apply an outside flux band centered in the bobbin window as shown in illustration. Overlap and solder ends of band to form a shorted turn. Attach wire item [4] to copper band and terminate to pin 7.
Assembly (2)	Apply 1 layer of tape item [5] around transformer as shown to insulate flux band. Remove pins 3, 4, 5, 8, 9, and 14. Cut pin 2 short. Dip varnish [9].

7.2.6 Winding Illustrations

For the purpose of these instructions, bobbin is oriented on winder such **General Note** that pins are on the left side (see illustration). Winding direction as shown is clockwise. Starting on pin 2, wind 30 turns of triple insulated wire item [3] in 1 layer, Wind remaining 9 turns back WD1: 1st Primary evenly across bobbin window, finish on pin 1. Apply 2 layers of tape item [5]. Insulation Using tape item [6], apply a 3 mm margin to pins side of bobbin. Match Margin height of WD2.

WD2: Secondary		Starting at pins 12 & 13, wind 25 trifilar turns of wire item [4] in 2 layers, finishing at pins 10 & 11.
Insulation		Apply 2 layers of tape item [5].
WD3: ½ Primary		Starting on pin 6, wind 30 turns of triple insulated wire item [3] in 1 layer, and finish on pin 2.
Insulation	Typ, J. deb; 2 this t is	Apply 3 layers of tape item [5].

Assembly (1)



Assemble gapped and ungapped core halves in bobbin, secure with tape. Using copper tape item [7], apply an outside flux band centered in the bobbin window as shown in illustration. Overlap and solder ends of band to form a shorted turn. Attach wire item [4] to copper band and terminate to pin 7.

Assembly (2)

Apply 1 layer of tape item [5] around transformer as shown to insulate flux band. Remove pins 3, 4, 5, 8, 9, and 14. Cut pin 2 short. Dip varnish [8].

7.3 Standby Transformer (T2) Specification

7.3.1 Electrical Diagram

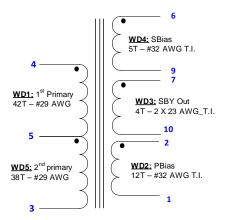


Figure 11 – Transformer Electrical Diagram.

7.3.2 Electrical Specifications

Electrical Strength	1 second, 60 Hz, from pins 1-5 to 6-10.	3000 VAC
Primary Inductance	Pins 4-3 all other windings open, measured at 100 kHz, 0.4 V_{RMS} .	1074 •H ±10%
Resonant Frequency	Pins 4-3, all other windings open.	1500 kHz (Min.)
Primary Leakage Inductance	Pins 4-3, with pins 7 and 10 shorted, measured at 100 kHz, $0.4 V_{\text{RMS}}$.	50 μH (Max.)

7.3.3 Material List

Item	Description
[1]	Core: EF25, TDK PC44 material or equivalent.
נייז	gap for inductance coefficient (A _L) of 202 nH/T ² .
[2]	Bobbin, EF25, Vertical, 10 Pins (5/5) Miles-Platts FE0100 w/ 10 pieces TBS601 terminal, PI
[Z]	Part # 25-00012-00.
[3]	Tape, Polyester film, 3M 1350F-1 or equivalent, 16.0 mm wide.
[4]	Tape, Polyester film, 3M 1350F-1 or equivalent, 14.9 mm wide.
[5]	Tape, Polyester web, 3M 44 or equivalent, 1.5 mm wide.
[6]	Wire, Magnet 28 AWG, solderable double coated.
[7]	Wire, Triple Insulated, Furukawa TEX-E or equivalent, #23 AWG.
[8]	Wire, Triple Insulated, Furukawa TEX-E or equivalent, #32 AWG.
[9]	Transformer Varnish, Dolph BC-359 or equivalent.

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7.3.4 Build Diagram

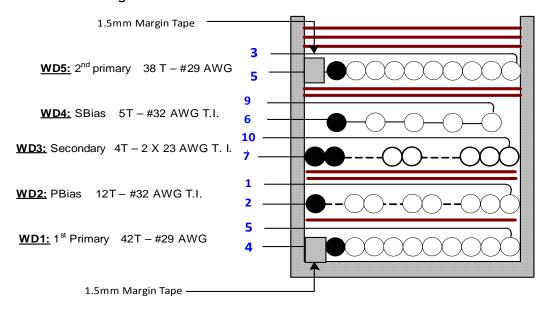


Figure 12 – Transformer Build Diagram.

7.3.5 Winding Instructions

General Note	Note For the purpose of these instructions, bobbin is oriented on winder such that pin sid is on the left side (see illustration). Winding direction as shown is clockwise.	
Margin	Apply 1.5 mm margin on pin side of bobbin using tape [5]. Match height of WDG 1.	
WD1: 1 st Primary	Starting at pin 4, wind 42 turns of wire item [6] in 1 layer. Finish at pin 5.	
Insulation	Use 1 layer of tape item [3] for insulation.	
WD2: PBias	Starting at pin 2, wind 12 turns of triple insulated wire item [8] in one layer. Finish at pin 1.	
Insulation	Use 2 layers of tape item [3] for insulation.	
WD3: Secondary	Starting at pin 9, wind 4 bifilar turns of triple insulated wire item [7] in one layer. Finish at pin 10.	
WD4: SBias	Starting on pin 6, wind 5 turns of triple insulated wire item [8] directly on top of WD3. Space turns evenly across bobbin width, and finish on Pin 9.	
Insulation	Use 2 layers of tape item [3] for insulation.	
Margin	Apply 1.5 mm margin on pins side of bobbin using tape [5]. Match height of WDG 4.	
WD5: 2 nd Primary	Starting at pin 5, wind 38 turns of wire item [6] in 1 layer. Finish at pin 3.	
Insulation	Use 3 layers of tape item [3] to secure the windings.	
Assembly	Grind core halves for specified primary inductance. Wrap one core half with 2 layers of tape item [4] as shown in illustrations. Insert the wrapped core in pin side of bobbin. Secure core halves with tape. Remove pin 8, cut pin 5 short. Dip varnish item [9].	

7.3.6 Transformer Illustrations

General Note	For the purpose of these instructions, bobbin is oriented on winder such that pin side is on the left side (see illustration). Winding direction as shown is clockwise.
Margin	Apply 1.5 mm margin on pins side of bobbin using tape [5]. Match height of WDG 1 & 2.
WD1: 1 st Primary	Starting at pin 4, wind 42 turns of wire item [6] in 1 layer. Finish at pin 5.

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Insulation	Use 1 layer of tape item [3] for insulation.
WD2: PBias	Starting at pin 2, wind 12 turns of triple insulated wire item [8] in one layer. Finish at pin 1.

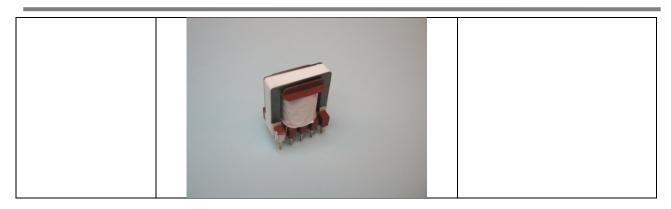
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Insulation	Use 2 layers of tape item [3] for insulation.
WD3: Secondary	Starting at pin 7, wind 4 bifilar turns of triple insulated wire item [7] in one layer. Finish at pin 10.



WD4: SBias	Starting on Pin6, wind 5 turns of triple insulated wire item [8] directly on top of WD3. Space turns evenly across bobbin width, and finish on pin 9.
Insulation	Use 2 layers of tape item [3] for insulation.
Margin	Apply 1.5 mm margin on pins side of bobbin using tape [5]. Match height of WDG 4.
WD4: 2 nd Primary	Starting at pin 5, wind 38 turns of wire item [6] in 1 layer. Finish at pin 3.

Insulation		Use 3 layers of tape item [3] to secure the windings.
Assembly	7mm	Grind core halves for specified primary inductance. Wrap one core half with 2 layers of tape item [4] as shown in illustrations. Insert the wrapped core in pin side of bobbin. Secure core halves with tape. Remove pin 8, cut pin 5 short. Dip varnish item [9].



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7.4 Main Output Choke (L4) Specification

7.4.1 Electrical Diagram

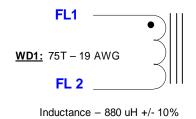


Figure 13 – Output Choke Schematic.

7.4.2 Material List

Item	Description
[1]	Core: Sendust Toroid 125 µ, 27.7 mm diameter, Mag-Inc 77930-A7 or equivalent.
[4]	Wire, Magnet, #19 AWG, solderable double coated.

7.4.3 Winding Illustration



Figure 14 – Finished Output Choke.

8 PFC Design Spreadsheet

Hiper_PFS-3_Boost_041715; Rev.0.7; Copyright Power Integrations 2015 Prower Integrations 2015 VACMIN VACMIN VACMIN VACMIN VACMIN VACMAX VACMAX VACMAX VACMAX VARDIN VARDIN	o i i o besigi					
Input Voltage Range	3_Boost_041715; Rev.0.7; Copyright Power Integrations 2015		INFO	OUTPUT	UNITS	Continuous Mode Boost Converter Design
VACMIN				1	1	
VACMIN VACMIN VACMAX A265 VAC Maximum AC input voltage per IC specifications; Line impedance not accounted. VBROWNIOUT 69 VAC Specifications; Line impedance not accounted. Expected Typical Brown-in Voltage per IC specifications; Line impedance not accounted. VBROWNIOUT 69 VAC Specifications; Line impedance not accounted. Expected Typical Brown-out voltage per IC specifications; Line impedance not accounted. VO 385 VDC Nominal olad voltage PO 341 341 W Nominal Output power 1. In So Hz Line frequency Maximum ambient temperature 1. 1. 1. 1. 1. 1. 1. 1. 1. 1	Input Voltage Range	Universal		Universal		
VACMAX 265	VACMIN			90	VAC	is performed at this voltage. To examine operation at other votlages, enter here, but enter fixed value
VBROWNIN 79	VACMAX			265	VAC	
VAC Specifications; Line impedance not accounted.	VBROWNIN			79	VAC	specifications; Line impedance not accounted.
PO 341 341 W Nominal Output power fL 50 Hz Line frequency TA Max 40 °C Maximum ambient temperature n 0,93 Enter the efficiency estimate for the boost converter at VACMIN. Should approximately match calculated efficiency in Loss Budget section VO_MIN 366 VDC Minimum Output voltage (efficiency in Loss Budget section) VO_RIPPLE_MAX 20 VDC Maximum Output voltage (in the Color of the Color of Pts. For Forted are color of Col	VBROWNOUT			69	VAC	
FL	VO			385	VDC	Nominal load voltage
TA Max	PO	341		341	W	Nominal Output power
Enter the efficiency estimate for the boost converter at VACMIN. Should approximately match calculated efficiency in Loss Budget section VO_MIN VO_RIPPLE_MAX VO_RIPPLE_MAX 20 VDC Minimum Output voltage WO_RIPPLE_MAX Holdup time WHOLDUP_MIN 310 VDC Minimum Output voltage ripple Holdup time Holdup time Enter "Yes" for Forced air cooling, Otherwise enter "No". Forced air cooling, Otherwise enter "No". Forced air reduces acceptable choke current density and core autopick core size KP_ACTUAL LPFC_TARGET D.520 LPFC_DESIRED (0 bias) LPFC_DESIRED (0 bias) D.508 Actual KP calculated from LPFC_ACTUAL LPFC_PEAK D.508 Actual KP calculated from LPFC_ACTUAL LPFC_PEAK D.508 Actual KP calculated from LPFC_ACTUAL LPFC_DESIRED (0 bias) Basic current parameters IAC_RMS A.07 A AC input RMS current at VACMIN and Full Power IOCP min Maximum Output voltage Whimum Output voltage Minimum Output voltage Minimum Output voltage input watch and individed individed in unsurent and provide at the peak of VACMIN and full power load at the peak of VACMIN Affects inductance value PFC inductance required to hit KP_TARGET at peak of VACMIN and full load LPFC_VALUE used for calculations. Leave blank to use LPFC_TARGET. Enter value to hold constant (also enter core selection) while changing VACMIN to examine brownout operation. Calculated inductance with rounded (integral) turns for powder core. Actual KP calculated from LPFC_ACTUAL LPFC_DESIRED (0 bias) Basic current parameters If examining brownout operation, over-ride autopick with desired device size Mode of operation of PFS. For Full Power "EFFICIENCY" to indicate efficiency mode enter "EIFICIENCY" to indicate efficiency mode IOCP min JOP MAX MAXIMUM Current limit Mode of operation in the post of the part of the provided at the provided and part of the part o	fL			50	Hz	Line frequency
No. Stock	TA Max			40	°C	Maximum ambient temperature
VO_RIPPLE_MAX	n			0.93		at VACMIN. Should approximately match calculated
HOLDUP 15 15 ms Holdup time VHOLDUP_MIN 310 VDC Minimum Voltage Output can drop to during holdup LINRUSH 40 A Maximum allowable inrush current Enter "Yes" for Forced air cooling. Otherwise enter "No". Forced air reduces acceptable choke current density and core autopick core size KP and INDUCTANCE KP_TARGET 0.520 0.520 Target ripple to peak inductor current ratio at the peak of VACMIN. Affects inductance value LPFC_TARGET (0 bias) 220 uH PFC inductance required to hit KP_TARGET at peak of VACMIN and full load LPFC_DESIRED (0 bias) 220 uH PFC inductance required to hit KP_TARGET at peak of VACMIN and full load LPFC_TARGET. Enter value to hold constant (also enter core selection) while changing VACMIN to examine brownout operation. Calculated inductance with rounded (integral) turns for powder core. KP_ACTUAL 0.508 Actual KP calculated from LPFC_ACTUAL LPFC_PEAK 220 uH Inductance at VACMIN, 90°. For Ferrite, same as LPFC_DESIRED (0 bias) Basic current parameters IAC_RMS 4.07 A AC input RMS current at VACMIN and Full Power load IO_DC 0.89 A Output average current/Average diode current PFS Parameters PFS Parameters PFS Part Number Auto PFS7528H If examining brownout operation, over-ride autopick with desired device size Mode of operation of PFS. For Full Power mode enter "Full Power" otherwise enter "EFFICIENCY" to indicate efficiency mode IOCP min 9.0 A Minimum Current limit IOCP max 9.9 A Maximum current limit	VO_MIN			366	VDC	
HOLDUP 15 15 ms Holdup time VHOLDUP_MIN 310 VDC Minimum Voltage Output can drop to during holdup LINRUSH 40 A Maximum allowable inrush current Enter "Yes" for Forced air cooling. Otherwise enter "No". Forced air reduces acceptable choke current density and core autopick core size KP and INDUCTANCE KP_TARGET 0.520 0.520 Target ripple to peak inductor current ratio at the peak of VACMIN. Affects inductance value LPFC_TARGET (0 bias) 220 uH PFC inductance required to hit KP_TARGET at peak of VACMIN and full load LPFC_DESIRED (0 bias) 220 uH PFC inductance required to hit KP_TARGET at peak of VACMIN and full load LPFC_TARGET. Enter value to hold constant (also enter core selection) while changing VACMIN to examine brownout operation. Calculated inductance with rounded (integral) turns for powder core. KP_ACTUAL 0.508 Actual KP calculated from LPFC_ACTUAL LPFC_PEAK 220 uH Inductance at VACMIN, 90°. For Ferrite, same as LPFC_DESIRED (0 bias) Basic current parameters IAC_RMS 4.07 A AC input RMS current at VACMIN and Full Power load IO_DC 0.89 A Output average current/Average diode current PFS Parameters PFS Parameters PFS Part Number Auto PFS7528H If examining brownout operation, over-ride autopick with desired device size Mode of operation of PFS. For Full Power mode enter "Full Power" otherwise enter "EFFICIENCY" to indicate efficiency mode IOCP min 9.0 A Minimum Current limit IOCP max 9.9 A Maximum current limit				20	VDC	
INRUSH Forced Air Cooling Yes Yes Yes Yes Forced Air Cooling Yes Yes Yes Yes Forced Air Cooling Yes		15		15	ms	Holdup time
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Forced Air Cooling Yes					Α	
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Target ripple to peak inductor current ratio at the peak of VACMIN. Affects inductance value	KP and INDUCTANCE	<u>l</u>				defisity and core autopick core size
LPFC_DESIRED (0 bias) LPFC_PEAK LPFC_PEAK LPFC_PEAK LPFC_DESIRED (0 bias) LPFC_DESIRED		0.520		0.520		peak of VACMIN. Affects inductance value
LPFC_DESIRED (0 bias) 220 uH LPFC_TARGET. Enter value to hold constant (also enter core selection) while changing VACMIN to examine brownout operation. Calculated inductance with rounded (integral) turns for powder core. KP_ACTUAL LPFC_PEAK D.508 Actual KP calculated from LPFC_ACTUAL Inductance at VACMIN, 90°. For Ferrite, same as LPFC_DESIRED (0 bias) Basic current parameters IAC_RMS AC input RMS current at VACMIN and Full Power load IO_DC D.89 A Output average current/Average diode current PFS Parameters PFS Parameters PFS Part Number Auto PFS7528H Operating Mode Full Power Full Power Full Power If examining brownout operation, over-ride autopick with desired device size Mode of operation of PFS. For Full Power mode enter "Full Power" otherwise enter "EFFICIENCY" to indicate efficiency mode IOCP min 9.0 A Minimum Current limit IOCP max Psypical current limit TOCP max Maximum current limit	LPFC_TARGET (0 bias)			220	uН	
LPFC_PEAK 220 uH Inductance at VACMIN, 90°. For Ferrite, same as LPFC_DESIRED (0 bias) Basic current parameters IAC_RMS 4.07 A AC input RMS current at VACMIN and Full Power load IO_DC 0.89 A Output average current/Average diode current PFS Parameters PFS Part Number Auto PFS7528H Operating Mode Full Power Full Power Full Power Full Power Full Power Full Power Full Power Full Power Full Power Full Power Full Power Full Power Full Power Full Power Full Power indicate efficiency mode IOCP typ 9.5 A Typical current limit IOCP max Maximum current limit	,				uH	LPFC_TARGET. Enter value to hold constant (also enter core selection) while changing VACMIN to examine brownout operation. Calculated inductance with rounded (integral) turns for powder core.
Basic current parameters IAC_RMS IAC_RMS AC input RMS current at VACMIN and Full Power load IO_DC PFS Parameters PFS Part Number Auto PFS7528H Operating Mode Full Power Full Power IOCP min IOCP typ PS Parameters LPFC_DESIRED (0 bias) AC input RMS current at VACMIN and Full Power load AC input RMS current at VACMIN and Full Power load AC input RMS current at VACMIN and Full Power load AC input RMS current at VACMIN and Full Power load AC input RMS current at VACMIN and Full Power load AC input RMS current at VACMIN and Full Power load A Output average current/Average diode current If examining brownout operation, over-ride autopick with desired device size Mode of operation of PFS. For Full Power mode enter "Full Power" otherwise enter "EFFICIENCY" to indicate efficiency mode IOCP min IOCP typ JOC A Minimum Current limit IOCP max AC input RMS current at VACMIN and Full Power load A Output average current/Average diode current If examining brownout operation, over-ride autopick with desired device size A Mode of operation of PFS. For Full Power enter "Full Power" otherwise enter "EFFICIENCY" to indicate efficiency mode IOCP min JOCP max A Maximum Current limit	KP_ACTUAL			0.508		
AC input RMS current at VACMIN and Full Power load IO_DC 0.89 A Output average current/Average diode current PFS Parameters PFS Part Number Auto PFS7528H Operating Mode Full Power A Minimum Current limit IOCP typ 9.5 A Typical current limit MAC input RMS current at VACMIN and Full Power load Note Power If examining brownout operation, over-ride autopick with desired device size Mode of operation of PFS. For Full Power mode enter "Full Power" otherwise enter "EFFICIENCY" to indicate efficiency mode IOCP max A C input RMS current at VACMIN and Full Power load If examining brownout operation, over-ride autopick with desired device size A Mode of operation of PFS. For Full Power mode enter "Full Power" otherwise enter "EFFICIENCY" to indicate efficiency mode IOCP min 9.0 A Minimum Current limit IOCP max A Maximum current limit	LPFC_PEAK			220	uH	
IO_DC	Basic current parameter	rs				
PFS Part Number Auto PFS7528H Operating Mode Full Power A Minimum Current limit IOCP typ 9.5 A Typical current limit IOCP max 9.9 A Maximum current limit						load
PFS Part Number Auto PFS7528H If examining brownout operation, over-ride autopick with desired device size Mode of operation of PFS. For Full Power mode enter "Full Power" otherwise enter "EFFICIENCY" to indicate efficiency mode IOCP min 9.0 A Minimum Current limit IOCP typ 9.5 A Typical current limit IOCP max 9.9 A Maximum current limit				0.89	Α	Output average current/Average diode current
Operating Mode Full Power IOCP min 9.0 A Minimum Current limit IOCP typ 9.5 A Typical current limit IOCP max 9.9 A Maximum current limit	PFS Parameters			<u> </u>		1
Operating Mode Full Power Full Power Full Power enter "Full Power" otherwise enter "EFFICIENCY" to indicate efficiency mode IOCP min 9.0 A Minimum Current limit IOCP typ 9.5 A Typical current limit IOCP max 9.9 A Maximum current limit	PFS Part Number	Auto		PFS7528H		with desired device size
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IOCP max 9.9 A Maximum current limit	IOCP min			9.0	A	
	IOCP typ			9.5	Α	
IP 7.41 A MOSFET peak current	IOCP max			9.9	Α	
	IP			7.41	A	MOSFET peak current

RDSON	RMS		3.42	Α	PFS MOSFET RMS current
FS_PK 96 KHz Estimated frequency of operation at crest of involtage (at VACMIN) voltage (at VACMIN) voltage (at VACMIN)					
FS_AVG 68					Estimated frequency of operation at crest of input
Covered at VACMIN Cov					Estimated average frequency of operation over line
PSW_LOSS_PFS S.1 W Estimated PFS switching losses					
PFS TOTAL S.5 W Total Estimated PFS losses TJ Max					
TJ Max Rth-JS					
Rth-JS 2.80 °C/W Maximum thermal resistance (Junction to hear Indicator) HEATSINK Theta-CA 3.15 °C/W Maximum thermal resistance of heatsink INDUCTOR DESIGN Basic Inductor Parameters Value of PFC inductor at zero current. This is value measured with LCR meter. For powder be different than LPFC. LP_TOL 10.0 % Tolerance of PFC Inductor Value (ferrite only) inductor at zero current. This is value measured with LCR meter. For powder be different than LPFC. LP_TOL 10.0 % Tolerance of PFC Inductor Value (ferrite only) inductor at zero current. This is value measured with LCR meter. For powder be different than LPFC. LP_TOL 10.0 % Tolerance of PFC Inductor value (ferrite only) inductor at zero current. This is value measured with LCR meter. For powder be different than LPFC. LP_TOL 10.0 % Tolerance of PFC Inductor value (ferrite only) inductor at zero current. This is value measured with LCR meter. For powder be different than LPFC. LP_TOL 10.0 % Tolerance of PFC Inductor value (ferrite only) inductor. LP_TOL 11.0 % Tolevance of PFC Inductor value (ferrite only) inductor. Core Or Toley Pow Inductor Perrite Enter "Sendust", "Pow Iron cores. Core All Alphance Inductor Pow Inductor Pow Inductor Pow Inductor Inductor Inductor P					
HEATSINK Theta-CA S.1.5					
Design					Maximum thermal resistance (Junction to heatsink)
Basic Inductor Parameters LPFC (0 Bias) 220 4 Walue of PFC inductor at zero current. This is value measured with LCR meter. For powder be different than LPFC. LP_TOL 10.0 4 Tolerance of PFC Inductor Value (ferrite only) is value measured with LCR meter. For powder be different than LPFC. 10.0 4 Tolerance of PFC Inductor Value (ferrite only) is value measured with LCR meter. For powder be different than LPFC. 10.0 4 Tolerance of PFC Inductor Value (ferrite only) is value measured with LCR meter. For powder be different than LPFC. 10.0 4 Tolerance of PFC Inductor Value (ferrite only) is value measured with LCR meter. This value measured with LCR meter. This is value measured with LCR meter. This v	EATSINK Theta-CA		3.15	°C/W	Maximum thermal resistance of heatsink
LPFC (0 Bias) 220 uH Value of PFC inductor at zero current. This is value measured with LCR meter. For powder be different than LPFC. LP_TOL 10.0 4.00 A Inductor RMS current (calculated at VACMIN Full Power Load) Material and Dimensions Core Type Ferrite Ferrite Ferrite Ferrite Select from 60u, 75u, 90u or 125 u for Sendu cores. Fixed at PC44/PC95 for Ferrite Cores. Fixed at PC44/PC95 for Ferr	NDUCTOR DESIGN				
LPFC (0 Bias) LP_TOL LP_TOL 10.0 % Tolerance of PFC Inductor Value (ferrite only) Inductor RMS current (calculated at VACMIN Full Power Load) Material and Dimensions Core Type Ferrite Core Material Auto PC44/PC95 Core Geometry Auto PQ PQ32/30 Core PQ32/30 Ae 161.00 mm^22 Core AL value Ve 12.00 Toriod only for Sendust and Powdered Iron; Inductor RMS current (particulated at VACMIN Full Power Load) MTT (EE/PQ) / ID (toroid) MLT BW 18.60 BP_TARGET (ferrite only) B_MAX PC44/PC95 10.00 10.00 10.00 M Toriod only for Sendust and Powdered Iron; Inductor Power Load, only for Sendust and Power Load, nominal inductance (ferrite only) According to the different table Power Load, divided by permeability at Ocurrent, at VACMIN Full Power Load, nominal inductance Ve Load (power Load, only for Sendust and Powdered Iron; Inductor Power Load, power Loa	asic Inductor Paramete	rs			
LP_TOL 10.0	PFC (0 Bias)		220	uH	Value of PFC inductor at zero current. This is the value measured with LCR meter. For powder, it will be different than LPEC
IL_RMS 4.00 A Inductor RMS current (calculated at VACMIN Full Power Load) Material and Dimensions Core Type Ferrite Ferrite Enter "Sendust", "Pow Iron" or "Ferrite" Core Material Auto PC44/PC95 Select from 60u, 75u, 90u or 125 u for Sendu cores. Fixed at PC44/PC95 for Ferrite cores. For End at PC44/PC95 for Ferrite cores. Fixed at PC44/PC95 for Ferrite core. For End at PC44/PC95 for Ferrite cores. Core and Power Load, for Ferrite cores. For End at PC44/PC95 for Ferrite cores. Core and Power Load, for Ferrite core. Core at Palacular for Ferrite core. Core at Palacular for Ferrite or Ferrite core. F	P TOL		10.0	%	
Material and Dimensions Core Type Ferrite Ferrite Ferrite Select from 60u, 75u, 90u or 125 u for Sendu cores. Fixed at PC44/PC95 for Ferrite cores. F. 52 material for Pow Iron cores. F. 22 material for Pow Iron cores. F. 22 material for Pow Iron cores. F. 23 material for Pow Iron cores. F. 24 material for Pow Iron cores. F. 25 material for Pow Iron cores. F. 27 material for Pow Iron cores. To Core and maximum tolerance inductance (ferrite only) drives turns and gap Flux and MMF calculations BP_TARGET (ferrite only) B_OCP (or BP) 3818 Gauss Gauss Full Power Load, ivided by permeability at O current (powder only) What prevent cores. Core for Sentite Cores. To Core and maximum tolerance inductance (ferrite only) drives turns and gap Full Power Load, divided by permeability at O current (powder only)				-	Inductor RMS current (calculated at VACMIN and
Core Type Ferrite Ferrite Enter "Sendust", "Pow Iron" or "Ferrite" Core Material Auto PC44/PC95 Select from 60u, 75u, 90u or 125 u for Sendu cores. Fixed at PC44/PC95 for Ferrite cores. F-52 material for Pow Iron cores. Core Geometry Auto PQ Toroid only for Sendust and Powdered Iron; I PQ for Ferrite cores. Core PQ32/30 Core part number Ocer part number Ae 161.00 mm^2 Core cross sectional area Le 74.60 mm Core mean path length AL 5140.00 nH/t^2 Core AL value Ve 12.00 cm^3 Core height/Height of window; ID if toroid MLT 67.1 mm Mean length per turn BW 18.60 mm Bobbin width LG 1.11 mm Gap length (Ferrite cores only) Flux and MMF calculations Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap B_OCP (or BP) 3818 Gauss Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap Target flux			7.00	Α	Full Power Load)
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Core Material Auto PC44/PC95 Core Geometry Auto PQ Auto Parent and PC49/PC95 for Ferrite cores. F -52 material for Pow Iron cores. Core Autoency Autou Autou PA Autou PCA Autou P	ore Type	Ferrite	Ferrite		
Core PQ32/30 PQ32/30 Core part number Ae 161.00 mm^2 Core cross sectional area Le 74.60 mm Core mean path length AL 5140.00 nH/t^2 Core AL value We 12.00 cm^3 Core volume HT (EE/PQ) / ID (toroid) 5.12 mm Core height/Height of window; ID if toroid MLT 67.1 mm Mean length per turn BW 18.60 mm Bobbin width LG 1.11 mm Gap length (Ferrite cores only) Flux and MMF calculations BP_TARGET (ferrite only) 3900 Gauss Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap B_OCP (or BP) 3818 Gauss Face of the density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap B_MAX 2730 Gauss Peak flux density at AC peak, VACMIN and Furly Power Load, nominal inductance """ """ """ """ """ """ """	ore Material	Auto	PC44/PC95		Select from 60u, 75u, 90u or 125 u for Sendust cores. Fixed at PC44/PC95 for Ferrite cores. Fixed at -52 material for Pow Iron cores.
Ae	ore Geometry	Auto	PQ		Toroid only for Sendust and Powdered Iron; EE or PQ for Ferrite cores.
Ae	ore	PO32/30	PO32/30		Core part number
Le 74.60 mm Core mean path length AL 5140.00 nH/t^2 Core AL value Ve 12.00 cm^3 Core volume HT (EE/PQ) / ID (toroid) 5.12 mm Core height/Height of window; ID if toroid MLT 67.1 mm Mean length per turn BW 18.60 mm Bobbin width LG 1.11 mm Gap length (Ferrite cores only) Flux and MMF calculations BP_TARGET (ferrite only) 3900 Gauss Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap B_OCP (or BP) 3818 Gauss Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap B_MAX 2730 Gauss Peak flux density at AC peak, VACMIN and Fupower Load, nominal inductance %μ at peak current vs. zero current, at VACMIN full Power Load, divided by permeability at 0 current (powder only)		. (32/33		mm^2	
AL 5140.00 nH/t^2 Core AL value Ve 12.00 cm^3 Core volume HT (EE/PQ) / ID (toroid) 5.12 mm Core height/Height of window; ID if toroid MLT 67.1 mm Mean length per turn BW 18.60 mm Bobbin width LG 1.11 mm Gap length (Ferrite cores only) Flux and MMF calculations BP_TARGET (ferrite only) 3900 Gauss Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap B_OCP (or BP) 3818 Gauss Gauss Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap B_MAX 2730 Gauss Peak flux density at AC peak, VACMIN and Further turns and gap Power Load, nominal inductance %μ at peak current vs. zero current, at VACMIN Full Power Load, divided by permeability at 0 current (powder only)					<u> </u>
Ve 12.00 cm^3 Core volume HT (EE/PQ) / ID (toroid) 5.12 mm Core height/Height of window; ID if toroid MLT 67.1 mm Mean length per turn BW 18.60 mm Bobbin width LG 1.11 mm Gap length (Ferrite cores only) Flux and MMF calculations BP_TARGET (ferrite only) 3900 Gauss Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap B_OCP (or BP) 3818 Gauss Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap B_MAX 2730 Gauss peak flux density at AC peak, VACMIN and Fu Power Load, nominal inductance μ_TARGET (powder only) N/A % μ at peak current vs. zero current, at VACMIN at 0 current (powder only)					
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MLT BW 18.60 mm Bobbin width LG 1.11 mm Gap length (Ferrite cores only) Flux and MMF calculations BP_TARGET (ferrite only) B_OCP (or BP) B_MAX 2730 Gauss Gauss Mean length per turn Bobbin width Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap B_MAX 2730 Gauss Gauss Full Power Load, nominal inductance %μ at peak current vs. zero current, at VACM Full Power Load, divided by permeability at 0 current (powder only) Set vs. zero current at VACMIN Full Power Letters are current at VACMIN Full Power					
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Flux and MMF calculations BP_TARGET (ferrite only) 3900 Gauss Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap B_OCP (or BP) 3818 Gauss Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap B_MAX 2730 Gauss peak flux density at AC peak, VACMIN and Fu Power Load, nominal inductance μ_TARGET (powder only) N/A % pat peak current vs. zero current, at VACMIN at 0 current (powder only)			_		
BP_TARGET (ferrite only) BP_TARGET (ferrite only) B_OCP (or BP) 3818 Gauss Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap B_MAX 2730 Gauss Gauss Peak flux density at AC peak, VACMIN and Fure power Load, nominal inductance %µ at peak current vs. zero current, at VACMIN Full Power Load, divided by permeability at 0 current (powder only) Peau vs. zero current at VACMIN Full Power Load.		_	1.11	111111	Gap length (Ferrite cores only)
BP_TARGET (ferrite only) 3900 Gauss maximum tolerance inductance (ferrite only) drives turns and gap Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) drives turns and gap B_MAX 2730 Gauss peak flux density at AC peak, VACMIN and Fure Power Load, nominal inductance μ_TARGET (powder only) N/A % Full Power Load, divided by permeability at 0 current (powder only)	ux and MMF calculation	iS	1		T
B_OCP (or BP) 3818 Gauss maximum tolerance inductance (ferrite only) drives turns and gap B_MAX 2730 Gauss peak flux density at AC peak, VACMIN and Further Power Load, nominal inductance μ_TARGET (powder only) N/A % Full Power Load, divided by permeability at 0 current (powder only) Pearly 5, zero current, at VACMIN Full Power Load.	P_TARGET (ferrite only)		3900	Gauss	maximum tolerance inductance (ferrite only) -
B_MAX 2730 Gauss peak flux density at AC peak, VACMIN and Fu Power Load, nominal inductance %μ at peak current vs. zero current, at VACMIN at VACMIN at VACMIN Full Power Load, divided by permeability at 0 current (powder only)	_OCP (or BP)		3818	Gauss	Target flux density at worst case: IOCP and maximum tolerance inductance (ferrite only) -
μ_TARGET (powder only) N/A % % Full Power Load, divided by permeability at 0 current (powder only) % **Powder only of the power Load in the powder only of the power Load in the powder only of the powder load in the powder only of the	_MAX		2730	Gauss	peak flux density at AC peak, VACMIN and Full
960 vs. zero current at VACMIN Full Dower I	_TARGET (powder only)		N/A	%	%μ at peak current vs. zero current, at VACMIN, Full Power Load, divided by permeability at 0
μ_MAX (powder only) N/A % (powder only)	_MAX (powder only)		N/A	%	%μ vs. zero current, at VACMIN Full Power LOAD
	OCP (powder only)		N/A	%	%μ vs. zero current, at IOCP_typ (powder only)
Current at which B_TEST and H_TEST are	- W		7	-	Current at which B TEST and H TEST are
I_TEST 9.5 A calculated, for checking flux at a current othe IOCP or IP; if blank IOCP_typ is used.	TEST		9.5	Α	calculated, for checking flux at a current other than IOCP or IP; if blank IOCP_typ is used.
B_TEST Gauss inductance	_TEST		3664	Gauss	
μ_TEST (powder only) N/A % relative permeability at I_TEST and typical inductance (powder only)			N/A	%	
Wire	/ire				
TURNS Inductor turns. To adjust turns, change BP_TARGET (ferrite) or µ_TARGET (powder)	JRNS		39		
ILRMS 4.00 A Inductor RMS current	RMS		4.00	Α	



Wire type	Litz		Litz		Select between "Litz" or "Magnet" for double coated magnet wire
AWG	38		38	AWG	Inductor wire gauge
Filar	60		60		Inductor wire number of parallel strands. Leave blank to auto-calc for Litz
OD (per strand)			0.102	mm	Outer diameter of single strand of wire
OD bundle (Litz only)			1.10	mm	Will be different than OD if Litz
DCR			0.12	ohm	Choke DC Resistance
P AC Resistance Ratio			1.11	Onn	Ratio of total Cu loss including HF ACR loss vs. assuming only DCR (uses Dowell equations)
J		Warning	8.22	A/mm^2	Current density is high, if copper loss is high use thicker wire, more strands, or larger core
FIT			50%	%	Percentage fill of winding window for EE/PQ core. Full window approx. 90%
Layers			2.1		Estimated layers in winding
Loss calculations		L	2.1		
BAC-p-p			1419	Gauss	Core AC peak-peak flux excursion at VACMIN, peak of sine wave
LPFC_CORE_LOSS			0.81	W	Estimated Inductor core Loss
LPFC_CORE_LOSS LPFC_COPPER_LOSS	1	1	2.20	W	Estimated Inductor core Loss Estimated Inductor copper losses
LPFC_COPPER_LOSS LPFC_TOTAL_LOSS			3.00	W	Total estimated Inductor Copper losses Total estimated Inductor Losses
			3.00	VV	Total estimated mudctor Losses
Built-in PFC Diode	1	1	TAITEDNIALA		DEC D: L D LN L
PFC Diode Part Number			INTERNAL1		PFC Diode Part Number
Туре			SPECIAL		PFD Diode Type
Manufacturer			PI		Diode Manufacturer
VRRM			530	V	Diode rated reverse voltage
IF			3	Α	Diode rated forward current
Qrr					high temperature
VF			1.47	V	Diode rated forward voltage drop
PCOND_DIODE			1.30	W	Estimated Diode conduction losses
PSW_DIODE			0.29	W	Estimated Diode switching losses
P_DIODE			1.59	W	Total estimated Diode losses
TJ Max			100	deg C	Maximum steady-state operating temperature
Rth-JS			3.00	degC/W	Maximum thermal resistance (Junction to heatsink)
HEATSINK Theta-CA			3.15	degC/W	Maximum thermal resistance of heatsink
Output Capacitor		•			
Output Capacitor	220		220	uF	Minimum value of Output capacitance
VO_RIPPLE_EXPECTED			13.8	V	Expected ripple voltage on Output with selected Output capacitor
T_HOLDUP_EXPECTED			16.8	ms	Expected holdup time with selected Output capacitor
ESR_LF		1	0.75	ohms	Low Frequency Capacitor ESR
ESR_HF			0.30	ohms	High Frequency Capacitor ESR
IC_RMS_LF		1	0.61	A	Low Frequency Capacitor RMS current
IC_RMS_HF		†	1.53	A	High Frequency Capacitor RMS current
CO_LF_LOSS			0.28	W	Estimated Low Frequency ESR loss in Output capacitor
CO_HF_LOSS			0.70	W	Estimated High frequency ESR loss in Output capacitor
Total CO LOSS			0.98	W	Total estimated losses in Output Capacitor
Input Bridge (BR1) and	Fuse (F1)				, ,
I^2t Rating			15.45	A^2*s	Minimum I^2t rating for fuse
Fuse Current rating			6.36	Α Α	Minimum Current rating of fuse
VF		1	0.90	V	Input bridge Diode forward Diode drop
IAVG		1	3.96	A	Input average current at 70 VAC.
PIV_INPUT BRIDGE		†	375	V	Peak inverse voltage of input bridge
PCOND_LOSS_BRIDGE		1	6.60	W	Estimated Bridge Diode conduction loss
CIN CIN			1.0	uF	Input capacitor. Use metallized polypropylene or film foil type with high ripple current rating
RT		<u> </u>	9.37	Ohmo	Input Thermistor value
ΓI			9.5/	ohms	Triput memistor value



D_Precharge		1N5407		Recommended precharge Diode
PFS3 small signal comp	onents			<u> </u>
C_REF		1.0	uF	REF pin capacitor value
RV1		4.0	MOhms	Line sense resistor 1
RV2		6.0	MOhms	Line sense resistor 2
RV3		6.0	MOhms	Typical value of the lower resistor connected to the V-PIN. Use 1% resistor only!
RV4		161.6	kOhms	Description pending, could be modified based on feedback chain R1-R4
C_V		0.495	nF	V pin decoupling capacitor (RV4 and C_V should have a time constant of 80us) Pick the closest available capacitance.
C_VCC		1.0	uF	Supply decoupling capacitor
C_C		100	nF	Feedback C pin decoupling capacitor
Power good Vo lower threshold VPG(L)		333	٧	Vo lower threshold voltage at which power good signal will trigger
PGT set resistor		333.0	kohm	Power good threshold setting resistor
Feedback Components		1 333.3		Towner good am content octaining resistor
R1		4.0	Mohms	Feedback network, first high voltage divider resistor
R2		6.0	Mohms	Feedback network, second high voltage divider resistor
R3		6.0	Mohms	Feedback network, third high voltage divider resistor
R4		161.6	kohms	Feedback network, lower divider resistor
C1		0.495	nF	Feedback network, loop speedup capacitor. (R4 and C1 should have a time constant of 80us) Pick the
D.F.		24.0		closest available capacitance.
R5		24.9	kohms	Feedback network: zero setting resistor
C2		1000	nF	Feedback component- noise suppression capacitor
Loss Budget (Estimated	at VACMIN)	0.40	14/	T
PFS Losses		8.49	W	Total estimated losses in PFS
Boost diode Losses		1.59	W	Total estimated losses in Output Diode
Input Bridge losses		6.60	W	Total estimated losses in input bridge module
Inductor losses		3.00	W	Total estimated losses in PFC choke
Output Capacitor Loss		0.98	W	Total estimated losses in Output capacitor
EMI choke copper loss		0.50	W	Total estimated losses in EMI choke copper
Total losses		20.66	W	Overall loss estimate
Efficiency		0.94		Estimated efficiency at VACMIN, full load.
CAPZero component sel	ection recommendat	tion		(O.1: 1) B
CAPZero Device		CAP005DG		(Optional) Recommended CAPZero device to discharge X-Capacitor with time constant of 1 second
Total Series Resistance (R1+R2)		0.48	k-ohms	Maximum Total Series resistor value to discharge X- Capacitors
EMI filter components r	ecommendation			
CIN_RECOMMENDED		1000	nF	Metallized polyester film capacitor after bridge, ratio with Po
CX2		680	nF	X capacitor after differencial mode choke and before bridge, ratio with Po
LDM_calc		151	uH	estimated minimum differencial inductance to avoid <10kHz resonance in input current
CX1		470	nF	X capacitor before common mode choke, ratio with Po
LCM		10	mH	typical common mode choke value
				estimated leakage inductance of CM choke, typical
LCM_leakage		30	uH	from 30~60uH
		30 220	рF	from 30~60uH typical Y capacitance for common mode noise suppression
LCM_leakage				typical Y capacitance for common mode noise
LCM_leakage CY1 (and CY2)	0.10	220	pF	typical Y capacitance for common mode noise suppression cal_LDM minus LCM_leakage, utilizing CM leakage



					copper loss
Note: CX2 can be placed be	tween CM ch				
design requirement.					

Note: If PFC inductor winding current density is higher than 6 A / mm² for forced air cooling, a "warning" will be generated by the design spreadsheet. Need for a larger wire cross section should be determined based on thermal test results. With sufficient cooling, higher current densities can be used safely. In the case of this design, the temperature rise as shown in Section 16 is acceptable.

10 Main / Standby Design Spreadsheet

HiperTFS2_Two- switch_Forward_041114; Rev.2.0; Copyright Power Integrations 2013	INPUT	INFO	ОИТРИТ	UNIT	HiperTFS2_041114_Rev2-0.xls; Two- switch Forward Transformer Design Spreadsheet
Hiper-TFS MAIN OUTPUT (H FORWAR	D STAGE)		
OUTPUT VOLTAGE AND CUI					
VMAIN	61.00		61.00	V	Main output voltage
IMAIN	4.59		4.59	Α	Main output current
VOUT2			0.00	V	Output2 voltage - enter zero or leave blank if none
IOUT2			0.00	Α	Output2 current - enter zero or leave blank if none
Post Regulated Output					
Post Regulator	NONE		NONE		Select post regulator from Mag-Amp, Buck, or NONE
V_SOURCE	NONE		NONE	V	Select source of input voltage for post regulator. Enter None if Post regulator not used.
VOUT3			0.00	V	Enter post regulator output voltage. Enter zero or leave blank if none
IOUT3			0.00	Α	Enter post regulator output current. Enter zero or leave blank if none
n_PR			1.00		Enter post regulator efficiency (Buck only)
Coupled Inductor (Low Pov	wer) derived	loutput			
VOUT4			0.00	V	Output choke derived (low power) output voltage (typically -12 V)
IOUT4			0.00	Α	Output choke derived (low power) output current
System Power					-
POUT(Main)			280.0	W	Total output power (Main converter)
POUT_PEAK(Main)	280.0		280.0	W	Peak Output power (Main converter). If there is no peak power requirement enter value equal to continuous power
POUT(Standby)			20.3	W	Continuous output power from Standby power supply
POUT_PEAK(Standby)			20.3	W	Peak output power from Standby section below
POUT(System Total)			300.3	W	Total system continuous output power
POUT_PEAK(System Total)			300.3	W	Total system peak output power
INPUT VOLTAGE AND UV/C	OV				· · · · · ·
CIN_MIN			37	uF	Minimum Input Capacitance to meet holdup time. To increase CMIN, increase T_HOLDUP
T_HOLDUP	1.0		1.0	ms	Holdup time
CIN_ACTUAL	220		220	uF	Select Actual Bulk Capacitor
CIN_ESR			0.30	Ω	Bulk capacitor ESR
IRMS_CIN			0.90	Α	RMS current through bulk capacitor
PLOSS_CIN			0.24	W	Bulk capacitor ESR losses
VMIN	360		360	٧	Minimum input voltage to guarantee output regulation at full load
VNOM	385		385	V	Nominal input voltage
VMAX			420	V	Maximum DC input voltage
RR			3.97	ΜΩ	R pin resistor
RL			3.97	ΜΩ	Line Sense resistor value (L-pin) - goal seek (VUV OFF) for std 1% resistor series
UV and OV thresholds					·
Clamp Section					
Clamp Selection	CLAMP TO RAIL				Select either "CLAMP TO RAIL" (default) or "CLAMP TO GND"
VCLAMP			150	٧	Asymmetric Clamp Zener Voltage



VDSOP		570	V	Estimated Maximum Hiper-TFS Drain voltage (at VOVOFF_MAX)
DUTY CYCLE VALUES (RE	GULATION)			
DVMIN		0.51		Duty cycle at minimum DC input voltage
DVNOM_GOAL	0.48	0.48		Target duty cycle at nominal input voltage (VNOM)
DVNOM		0.47		Duty cycle at nominal DC input voltage
DVMAX		0.43		Duty cycle at maximum DC input voltage
DOVOFF MIN		0.39		Duty cycle at over-voltage DC input voltage (DOVOFF_MIN)
Maximum Duty Cycle val	LIOS			(DOVOFF_MIN)
DMAX UVOFF MIN	lues	0.65		Max duty cycle clamp at VUVOFF_MIN
DMAX_OVOIT_ININ		0.59		Max duty cycle clamp at VOVOT1_MIN
DMAX_VNOM		0.56		Max duty clamp cycle at VNOM
DMAX_VMAX		0.52		Max duty clamp cycle at VMAX
DMAX_OVOFFMIN DEVICE VARIABLES		0.46		Max duty clamp cycle at VOVOFF_MAX
	TEC270/	TEC7706	•	Colored HistoryTEC desides
Device	TFS7706	TFS7706	1.11=	Selected HiperTFS device
Select Frequency mode	66	66	kHz	Select Frequency mode.
ILIMIT_MIN		4.05	A	Device current limit (Minimum)
ILIMIT_TYP		4.36	Α	Device current limit (Typical)
ILIMIT_MAX		4.67	Α	Device current limit (Maximum)
fSMIN		62,000	Hz	Device switching frequency (Minimum)
fS		66,000	Hz	Device switching frequency (Typical)
fSMAX		70,000	Hz	Device switching frequency (Maximum)
KI	0.9	0.9		Select Current limit factor (KI=1.0 for default ILIMIT, or select KI=0.9 or KI=0.7)
R(FB)		1740	kΩ	Feedback Pin Resistor value
ILIMIT SELECT		3.65	Α	Selected current limit
RDS(ON)		3.06	Ω	Sum of Rds(on) of high and low-side MOSFETs at 100°C
VDS		4.39	V	HiperTFS full-load average on-state Drain to Source Voltage (sum for both MOSFETs)
Main MOSFET losses		<u>'</u>	l	
MAIN TRANSFORMER				
Transformer core selection		FEDOR		
Core Type	EER35	EER35	4.0	Selected core type
AE		1.07	cm^2	Core effective cross sectional area
LE		9.08	cm	Core Effective Path Length
AL		2770	nH/T^2	Ungapped Core Effective Inductance
BW		26.1	mm	Bobbin Physical Winding Width
B_HT		5.52	mm	Height of bobbin (to calculate fit)
B_WA		1.44	cm^2	Bobbin Winding area
М		4.5	mm	Bobbin safety margin tape width (2 * M = Total Margin)
Primary Inductance				
LMAG_MAX		105.3	mH	Max LMAG to hit min zero-load resonant frequency, calculated from C_PRI. Do not exceed.
LMAG		12.7	mH	Estimated magnetizing inductance of transformer; may be lower than LMAG_MAX due to minimum gap size of 0.05 mm. Enter actual value.
GAP		0.00	mm	gap calculatedfrom LMAG
FRES_SYS	173	173	kHz	Total XFMR + system resonant frequency; enter value along with actual LMAG
C_SYS		67	pF	Estimated total XFMR + Sys parasitic cap reflected to primary, calc'd from LMAG and FRES
Diode Vf Selection				•
Turns				



NMAIN	1	I	25	turno	Main rounded turns
NS2			N/A	turns	2nd output number of turns
NS2			IN/A	turns	Approximate Output2 voltage with NS2 = 0
VOUT2 ACTUAL			0.0	V	turns (AC stacked secondary). VDMAIN and VDOUT2 affect this.
NP			69	turns	Primary rounded turns. NMAIN and DVNOM_GOAL affect this.
HI SIDE BIAS WINDING (optional)	No		No		Can be used to eliminate pulse skipping at light load 132 kHz when zero transformer gap; better efficiency than adding gap
VBIAS				V	DC bias voltage from main transformer optional aux winding
NBIAS				turns	VBias rounded turns
VBIAS_ACTUAL				V	Vbias not used
Flux calculations					
BM_MAX			2299	Gauss	Peak positive flux density at nominal switching frequency
BM PK-PK			3483	Gauss	Peak-peak flux density at nominal conditions. Used to calculate core losses
BP_MAX			2938	Gauss	Max transient positive flux density at Vmax (limited by DVMAX clamp)
BP PK-PK			4452	Gauss	Max transient peak-peak flux density at Vmax (limited by DVMAX clamp)
TRANSFORMER LOSSES A	AND FIT ESTI	MATE			
Core loss		1		1	
Core material	PC95		PC95		Core material
core_loss_multiplier			23.97		Core Loss coefficient
f_coeff			1.56		Core Loss Frequency co-efficient
BAC_coeff			2.89		Core Loss AC flux density co-efficient
specific core loss			105	mW/cc	Core loss per unit volume
core volume			9.72	cm^3	Volume of core
core loss Primary Winding Fit and	losses	<u> </u>	1.02	W	Core loss
L	103303		3.0	layers	Transformer primary layers (split primary recommended)
OD_PRI			0.57	mm	Primary winding diameter
FILAR_PRI			1.0	strands	Number of parallel strands of wire (primary)
MLT_PRI			6.14	cm	Mean length per turn
DCR_PRI			372	mΩ	DC resistance of primary winding
PCOND_PRI			0.54	W	Conduction loss in primary winding
FILL_PRI			12	%	Fill factor (primary only)
Secondary Winding 1 (lov	wer winding \	when AC sta	icked)		
VOUT			61.0	V	Specified voltage for this winding
NS1			25.0	turns	Number of turns
IRMS_SEC1			4.0	A	RMS current through winding
Foil/Wire	WIRE		WIRE	foil/wire	Select FOIL or WIRE for winding
OD/Thickness	-		0.36576	mm	Wire diameter or Foil thickness
FILAR_SEC1	3		3.00	strands	Number of parallel strands (wire selection only)
SEC1_WIDTH			N/A	mm	Foil Width (Applicable if FOIL winding used)
SEC1_MLT			6.14	cm	Mean length per turn
DCR_SEC1			107.62	mΩ	DC resistance of secondary winding
PCOND_SEC1	-		1.68	W	Conduction loss in secondary winding
FILL_SEC1		libor AO -:	5	%	Fill factor (secondary 1 only)
Secondary Winding 2 (up VOUT	per winding v	wnen AC sta		1 1/	Charified voltage for this winding
NS2	+		0.0	turns	Specified voltage for this winding Number of turns
IRMS_SEC2	+		0.0	turns	RMS current through winding
Foil/Wire	FOIL		FOIL	A foil/wire	Select FOIL or WIRE for winding
OD/Thickness	FUIL		0.125	foil/wire mm	Wire diameter or Foil thickness
FILAR_SEC2			N/A	strands	Number of parallel strands (wire selection
I TLAN_SLCZ		<u> </u>	IN/A	ou ai lus	manuer or paraller straints (wire selection)



					only)
SEC2_WIDTH			18.0	mm	Foil Width (Applicable if FOIL winding used)
SEC2_MLT			6.14	cm	Mean length per turn
DCR_SEC2			0.00	mΩ	DC resistance of secondary winding
PCOND_SEC2			0.00	W	Conduction loss in secondary winding
FILL_SEC2			0	%	Fill factor (secondary 1 only)
Fill Factor and losses of ma	ain transforr	ner	-		
FILL_TOTAL			18	%	Total transformer fill factor
TOTAL_CU_LOSS			2.22	W	Total copper losses in transformer
TOTAL_CORE_LOSS			1.02	W	Total core losses in transformer
TOTAL_TRF_LOSS			3.24	W	Total losses in transformer
CURRENT WAVESHAPE PAI	RAMETERS				
IP			2.30	Α	Peak primary current at Full Load, VNOM
IP_PEAK			2.30	Α	Peak primary current at Peak Load and VNOM
IPRMS(NOM)			1.21	Α	Primary RMS current at Full Load, VNOM
IMAG			0.22	Α	Peak magnetizing current at VMIN
OUTPUT INDUCTOR	,	,			
KDI_ACTUAL		Warning	0.50		!!! Warning. KDI_ACTUAL too high. Increase NMAIN_INDUCTOR
Turns					-
POWDER TURNS MULTIPLIER	3.00		3.0		Powder only. Multiplier factor between main number of turns in transformer and inductor (default value = 3 for 66kHz or 4 for 132kHz).
NMAIN_INDUCTOR			75.0	turns	Main output inductor number of turns - affected by powder turns multiplier or ferrite Target BM
NOUT2_INDUCTOR				turns	Output 2 inductor number of turns
NOUT4_INDUCTOR			N/A	turns	Output 4 number of turns (low power)
Inductance and flux		•			
LMAIN_ACTUAL			229.4	uH	Estimated inductance of main output at full load
LOUT_2			0.0	uH	Estimated inductance of auxiliary output at full load
BM_IND			2385	gauss	DC component of flux density
BAC_IND			575	gauss	AC component of flux density
Core Selection					
Core Type	Kool Mu 125u		Kool Mu 125u		Select core type
Core	Auto		77930(O.D)= 27.7		Output choke core size - verify on bench
AE			65.4	mm^2	Core Effective Cross Sectional Area
LE			63.5	mm	Core Effective Path Length
AL			157.0	nH/T^2	Ungapped Core Effective Inductance
BW			44.3	mm	Bobbin Physical Winding Width
VE			4150	mm^3	Volume of core
Powder cores (Sendust and	d Powdered	Iron) Cores			
MUR			125		Relative permeability of material at 0 bias
Н			60.2	AT/cm	Magnetic field strength
MUR_RATIO			0.26		Ratio of permeability at full load divided by initial permeability
LMAIN_0bias			883.1	uH	Estimated inductance of main output with 0 DC bias
Ferrite Cores					
LG			N/A	mm	Gap length of inductor cores
Target BM	<u> </u>		N/A	Gauss	Target maximum flux density
Choke wires		1			
Total number of layers	<u> </u>		1.67	layers	Total number of layers for chosen toroid
IRMS_MAIN			4.60	Α	RMS current through main inductor



IRMS_AUX MIG MAIN 19 AWG MAIN 19 AWG MAIN 100 1 strands Number of parallel strands for main inductor winding wire gauge Do MAIN 100 1 strands Number of parallel strands for main output. REC_MAIN AC Resistance Ratio (Main) CMA_MAIN 1.00 AC Resistance Ratio (Main) CMA_MAIN 1.00 AC Resistance Ratio (Main) CMA_MAIN 1.00 CMA_MAIN 1.00 CMA_MAIN 1.00 AWG Aux inding wire gauge outer diameter. CMA_MAIN 1.00 CMA_MAIN 1.00 CMA_MAIN 1.00 AWG Aux winding wire gauge outer diameter. CMA_MAIN 1.00 AWG Aux winding wire gauge outer diameter. CMA_MAIN 1.00 AWG Aux winding wire gauge outer diameter. CMA_MAIN 1.00 AWG Aux winding wire gauge outer diameter. CMA_MAIX 1.00 CMA_MILINFO Resistance of wire for auxiloutor winding and the companies of the for auxiloutor winding and the companies of the		1		I	-	Luindings
AWG MAIN	TDMC ALIV			0.00	Δ.	windings
OD. MAIN 0.98 mm Main winding wire gauge outer diameter FILAR_MAIN 1.00 1 strands Number of parallel strands or main output. RDC_MAIN 77.34 mΩ Resistance of wire for main inductor winding AC Resistance Ratio (Main) 6.94 Carent denote clusing Downel curves) CMA_MAIN 281 CMA Circ mils per amp for main inductor winding J, MAIN 6.99 A/mm² Current density in main inductor winding AWG_AUX 0 AWG Aux winding wire gauge outer diameter DO, AUX N/A mm Aux link winding wire gauge outer diameter FILAR_AUX 2 strands Number of parallel strands for aux output. FILAR_AUX 2 strands Number of parallel strands for aux output. CDC_AUX 0.00 mΩ Resistance of wire for aux inductor winding. AC Resistance Ratio (Aux) 0.00 CMA Will Info. Low CMA may cause overheating. CMA_AUX Info 0 CMA Will Info. Low CMA may cause overheating. CMOSE 0 CMA <						
FILAR_MAIN						
Recistance Ratio (Main) Resistance of wire for main inductor winding		1.00				
RUC_MAIN	FILAR_MAIN	1.00		1	strands	
AN Resistance (using Dowell curves) OCAN MAIN 281 CMA Cir mils per amp for main inductor winding J MAIN 6.09 A/mm^22 Current density in main inductor winding AWG AUX N/A N/A MM AUX MIGH MIX OD AUX FILAR AUX N/A CD MIX Resistance (wing for aux output RDC, AUX ROC, AUX ROC, AUX OD MIX ROC, AUX ROC, AUX ROC, AUX OD MIX RESISTANCE OF WINDING WING gauge outer diameter RDC, AUX ROC, AUX OD MIX RESISTANCE OF WINDING WING GAUX OUTPUT RATIO OF CMA AUX Info CMA, AUX Info CMA AVM MIX Info CMA AVM MIX Info CMA AVM MIX Info CMA AVM MIX Info COPPER MAIN INfo COPPER MAIN	RDC_MAIN			77.34	mΩ	winding
CMA MAIN 6.09 A/mm^2 2 2 2 2 2 2 2 2 2	AC Resistance Ratio (Main)			6.94		
J. MAIN 6.09 A/mm^2 Current density in main inductor winding AWG AUX 0	CMA MAIN			281	CMA	
AWG AUX DO AUX N/A mm Auxiliary winding wire gauge outer diameter FILAR AUX RDC AUX N/A mm Auxiliary winding wire gauge outer diameter FILAR AUX CR CRESISTANCE (AUX) DO 00 RESISTANCE (Using Dowell curve) Resistance (Jusing Dowell curve) Resistance of total resistance (AC + DC) to the Curve Resistance (Jusing Dowell curve) Resistance of total resistance (AC + DC) to the Curve Resistance (Jusing Dowell curve) Resistance of total resistance (AC + DC) to the Curve Resistance (Jusing Dowell curve) Resistance of total resistance (AC + DC) to the Curve Resistance (Jusing Dowell curve) Resistance of total resistance (AC + DC) to the Curve Resistance	J_MAIN			6.09	A/mm^2	Current density in main inductor winding
DAJUX N/A mm						
FILAR_AUX 2 strands Number of parallel strands for aux output. PROC_AUX 0.00 m\tilde{\text{D}} Resistance of wire for aux inductor winding. Ratio of total resistance (AC + DC) to the DC resistance (Ling Dowell curves)				N/A	mm	
REC_ALIX 0.00 m2 Resistance of wire for aux inductor winding AC Resistance Ratio (Aux) 0.00 Ratio of total resistance (AC + DC) to the DC resistance (using Dowell curves) 11 Info. Low CMA may cause overheating. Very CMA_AUX 0.00 A/mm^2 Current density in auxiliary winding Choke Losses COPPER_MAIN 0.64 W Copper loss in main inductor winding PCOPER_MAIN 0.66 A Copper loss in auxiliary windings PCOPER_MAIN 0.66 A Freewheeling diode RMS current at nominal input voltage Copper loss in auxiliary windings Copper loss Copper loss in auxiliary windings Copper loss Copper loss in auxiliary windings Copper loss Copper						
AC Resistance Ratio (Aux) AC Resistance Ratio (Aux) De Pestance (AC + DC) to the De Pestance (AC + DC						
CMA_AUX Info 0 CMA !!! Info. Low CMA may cause overheating. J_AUX 0.00 A/mm^2 Current density in auxiliary winding Choke Losses COPPER MAIN 1.64 W Copper loss in main inductor winding COPPER, AUX 0.00 W Copper loss in main inductor winding COPPER, AUX 0.00 W Copper loss in aux inductor winding COPPER, AUX 0.00 W Copper loss in aux inductor winding COPPER, AUX 0.00 W Copper loss in aux inductor winding COPPER, AUX 0.00 W Copper loss in aux inductor winding COPPER, AUX 0.00 W Copper loss in aux inductor winding COPPER, AUX 0.00 W Copper loss in aux inductor winding COPPER, AUX 0.00 W Copper loss in aux inductor winding COPPER, AUX 0.00 W Copper loss in aux inductor winding COPPER, AUX 0.00 W Copper loss in aux inductor windings COPPER, AUX 0.00 W Copper loss in aux inductor windings COPPER, AUX 0.00 W Copper loss in aux inductor windings COPPER, AUX 0.00 W Copper loss in aux inductor windings COPPER, AUX 0.00 W Copper loss in aux inductor winding COPPER, AUX 0.00 W Copper loss in aux inductor winding COPPER, AUX 0.00 W Copper loss in aux inductor winding COPPER, AUX 0.00 A Full load forward diode RMS current at nominal input voltage COPPER, AUX 0.00 A Full load forward diode COPPER, AUX 0.00 A COPPER, AUX 0.00 A Full load forward diode COPPER, AUX 0.00 A COPPER, AU	AC Resistance Ratio (Aux)				11132	Ratio of total resistance (AC + DC) to the
DAUX DAUX DAVA		+				
Choke Losses PCOPPER_MAIN	CMA_AUX		Info	_		Verify acceptable temperature rise
PCOPPER_MAIN 1.64 W Copper loss in main inductor winding PCOPPER_AUX 0.00 W Copper loss in aux inductor windings PCOPER 0.62 W Total core loss Total core loss PTOTAL_IND 2.26 W Total core loss Total core loss PTOTAL_IND Total core loss Total core loss PTOTAL_IND Total core loss Total core loss PTOTAL_IND Total core loss Total cores in output choke SECONDARY OUTPUT DIODE PARAMETERS	·	<u> </u>		0.00	A/mm^2	Current density in auxiliary winding
PCOPPER_AUX	Choke Losses	1				
PEORE 0.62 W Total core loss PTOTAL_IND 2.26 W Total losses in output choke SECONDARY OUTPUT DIODE PARAMETERS	_	1		-	W	
PTOTAL_IND 2.26 W Total losses in output choke SECONDARY OUTPUT DIODE PARAMETERS Main Output ISFWDRMS 3.95 A Full load forward diode RMS current at nominal input voltage ISCATCHRMS 4.16 A Freewheeling diode RMS current at nominal input voltage IDAVMAINF 2.33 A Worst case average current of forward rectifier at VMIN (single device rating) IDAVMAINC 2.60 A Worst case average current of freewheeling diode at VMAX(single device rating) IRMSMAIN 0.66 A Warimum RMS current, Main output capacitor PD_LOSS_MAIN 2.30 W Conduction loss of forward diode Second Output ISFWD2RMS 0.00 A Full load forward diode RMS current at nominal input voltage ISCATCH2RMS 0.00 A Freewheeling diode RMS current at nominal input voltage IDAVOUT2F 0.00 A Worst case average current of freewheeling diode at VMAX(single device rating) IRMSOUT2 0.00 A Worst case average current of forward rectifier at VMIN (single device rating) IRMSOUT2 0.00 A Worst case average current of forward rectifier at VMIN (single device rating) IRMSOUT2 0.00 A Worst case average current of freewheeling diode at VMAX(single device rating) IRMSOUT2 0.00 A Maximum RMS current, Main output capacitor PD_LOSS_OUT2 0.00 W Conduction loss of forward diode Diode Derating VPIVMAINF 1.00 206.5 V Main Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVMINC 1.00 0.0 V Worst Case average current of freewheeling diode at VMAX(single device rating) VPIVOUT2F 1.00 0.0 V Worst Case average current of freewheeling diode at VMAX(single device rating) VPIVOUT2F 1.00 0.0 V Worst Case average current of freewheeling diode at VMAX(single device rating) VPIVOUT2F 1.00 0.0 W Conduction loss of forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2C 1.00 0.0 W Worst Case average current of the voltage (at VDSOP), including derating VPIVOUT2C 1.00 0.0 W Worst Case average current of the voltage (at VDSOP), including derating VPIVOUT3C 1.00 0.0 W Worst Case average current o	PCOPPER_AUX			0.00	W	Copper loss in aux inductor windings
SECONDARY OUTPUT DIODE PARAMETERS 3.95 A Full load forward diode RMS current at nominal input voltage ISCATCHRMS 4.16 A Freewheeling diode RMS current at nominal input voltage IDAVMAINF 2.33 A Worst case average current of forward rectifier at VMIN (single device rating) IDAVMAINC 2.60 A Worst case average current of freewheeling diode at VMAX(single device rating) IMMSMAIN 0.66 A Maximum RMS current, Main output capacitor PD_LOSS_MAIN 2.30 W Conduction loss of forward diode ESCATCH2RMS 0.00 A Full load forward diode RMS current at nominal input voltage IDAVOUT2F 0.00 A Freewheeling diode RMS current at nominal input voltage IDAVOUT2C 0.00 A Maximum RMS current forward IDAVOUT2C 0.00 A Maximum RMS current, Main output IDAVOUT2C 0.00 W Conduction loss of forward diode IDAVOUT2C	PCORE			0.62	W	Total core loss
SECONDARY OUTPUT DIODE PARAMETERS 3.95 A Full load forward diode RMS current at nominal input voltage ISCATCHRMS 4.16 A Freewheeling diode RMS current at nominal input voltage IDAVMAINF 2.33 A Worst case average current of forward rectifier at VMIN (single device rating) IDAVMAINC 2.60 A Worst case average current of freewheeling diode at VMAX(single device rating) IMMSMAIN 0.66 A Maximum RMS current, Main output capacitor PD_LOSS_MAIN 2.30 W Conduction loss of forward diode ESCATCH2RMS 0.00 A Full load forward diode RMS current at nominal input voltage IDAVOUT2F 0.00 A Freewheeling diode RMS current at nominal input voltage IDAVOUT2C 0.00 A Maximum RMS current forward IDAVOUT2C 0.00 A Maximum RMS current, Main output IDAVOUT2C 0.00 W Conduction loss of forward diode IDAVOUT2C	PTOTAL_IND			2.26	W	Total losses in output choke
ISFWDRMS 3.95	SECONDARY OUTPUT DIO	DE PARAMET	TERS	!		
ISFWDRMS 3.95	Main Output					
IDAVMAINF IDAVMAINF IDAVMAINF IDAVMAINF IDAVMAINC IDAMMAINC	ISFWDRMS			3.95	А	
IDAVMAINF 1.00 1	ISCATCHRMS			4.16	А	Freewheeling diode RMS current at nominal
IDAVMAINC 2.60 A Worst case average current of freewheeling diode at VMAX(single device rating) IRMSMAIN 0.66 A Maximum RMS current, Main output capacitor PD_LOSS_MAIN 2.30 W Conduction loss of forward diode Second Output ISFWD2RMS 0.00 A Full load forward diode RMS current at nominal input voltage ISCATCH2RMS 0.00 A Freewheeling diode RMS current at nominal input voltage IDAVOUT2F 0.00 A Worst case average current of forward rectifier at VMIN (single device rating) IDAVOUT2C 0.00 A Worst case average current of forward rectifier at VMIN (single device rating) IRMSOUT2 0.00 A Maximum RMS current, Main output capacitor PD_LOSS_OUT2 0.00 A Maximum RMS current, Main output capacitor PD_LOSS_OUT2 0.00 W Conduction loss of forward diode Diode Derating VPIVMAINF 1.00 206.5 V Main Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2F 1.00 0.0 V Output2 Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2C 1.00 N/A V Bias output rectifier peak-inverse voltage (at VDSOP), including derating VPIVOUT2C 1.00 N/A V Bias output rectifier peak-inverse voltage (at VDSOP), including derating	IDAVMAINF			2.33	А	Worst case average current of forward
IRMSMAIN D.66 A Maximum RMS current, Main output capacitor Conduction loss of forward diode Second Output ISFWD2RMS D.00 A Full load forward diode RMS current at nominal input voltage ISCATCH2RMS D.00 A Freewheeling diode RMS current at nominal input voltage IDAVOUT2F D.00 A Worst case average current of forward rectifier at VMIN (single device rating) IDAVOUT2C D.00 A Worst case average current of freewheeling diode at VMAX(single device rating) IRMSOUT2 D.00 A Maximum RMS current, Main output capacitor PD_LOSS_OUT2 D.00 A Maximum RMS current, Main output capacitor PD_LOSS_OUT2 D.00 W Conduction loss of forward diode Diode Derating VPIVMAINF D.00 DIS2.2 V Main Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2F D.00 D.00 V Output2 Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2C D.00 N/A VPIVOUT2C D.00 N/A V Bias output rectifier peak-inverse voltage (at VDSOP), including derating VPIVOUT2C DIOD DIOD DIOD DIOD DIOD DIOD DIOD DIO	IDAVMAINC			2.60	А	Worst case average current of freewheeling
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Second Output	DD LOCC MAIN	+		2.20	14/	
ISFWD2RMS 0.00 A Full load forward diode RMS current at nominal input voltage ISCATCH2RMS 0.00 A Freewheeling diode RMS current at nominal input voltage IDAVOUT2F 0.00 A Worst case average current of forward rectifier at VMIN (single device rating) IDAVOUT2C 0.00 A Worst case average current of freewheeling diode at VMAX(single device rating) IRMSOUT2 0.00 A Maximum RMS current, Main output capacitor PD_LOSS_OUT2 0.00 W Conduction loss of forward diode Diode Derating VPIVMAINF 1.00 206.5 V Main Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVMAINC 1.00 152.2 V Main Catch Diode peak-inverse voltage (at VOVOFF_MAX), including derating VPIVOUT2F 1.00 0.0 V Output2 Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2C 1.00 0.0 V Output2 Catch Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2C 1.00 N/A V Bias output rectifier peak-inverse voltage (at VDSOP), including derating		1		2.30	vv	Conduction loss of forward diode
ISCATCH2RMS IDAVOUT2F IDAVOUT2F IDAVOUT2C IDAVOUT2C IDAVOUT2C IRMSOUT2 IRMSOUT3 IRMSOUT2 IRMSOUT2 IRMSOUT3 IRMSOUT4 IRMSOUT5 IRMSOUT5 IRMSOUT5 IRMSOUT5 IRMSOUT6 IRMSOUT6 IRMSOUT7 IRMSOUT7	ISFWD2RMS			0.00	A	
IDAVOUT2F IDAVOUT2F IDAVOUT2C		1				·
IDAVOUT2C IRMSOUT2 IRMSO	ISCATCH2RMS			0.00	А	input voltage
IRMSOUT2 0.00 A diode at VMAX(single device rating) Maximum RMS current, Main output capacitor PD_LOSS_OUT2 0.00 W Conduction loss of forward diode Diode Derating VPIVMAINF 1.00 206.5 V Main Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVMAINC 1.00 152.2 V Main Catch Diode peak-inverse voltage (at VOVOFF_MAX), including derating VPIVOUT2F 1.00 0.0 V Output2 Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2C 1.00 0.0 V Output2 Catch Diode peak-inverse voltage (at VOVOFF_MAX), including derating VPIVOUT2C 1.00 N/A V Bias output rectifier peak-inverse voltage (at VDSOP), including derating	IDAVOUT2F			0.00	Α	
IRMSOUT2 Diode Derating VPIVMAINF 1.00 206.5 V Main Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2F 1.00 0.00 V Main Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2F 1.00 0.0 V Output2 Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2C 1.00 0.0 V Output2 Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2C 1.00 N/A V Bias output rectifier peak-inverse voltage (at VDSOP), including derating	IDAVOUT2C			0.00	А	
PD_LOSS_OUT2 Diode Derating VPIVMAINF 1.00 206.5 V Main Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVMAINC 1.00 152.2 V Main Catch Diode peak-inverse voltage (at VOVOFF_MAX), including derating VPIVOUT2F 1.00 0.0 V Output2 Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2C 1.00 0.0 V Output2 Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2C 1.00 N/A V Bias output rectifier peak-inverse voltage (at VDSOP), including derating	IRMSOUT2			0.00	А	Maximum RMS current, Main output
Diode Derating VPIVMAINF 1.00 206.5 V Main Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVMAINC 1.00 152.2 V Main Catch Diode peak-inverse voltage (at VOVOFF_MAX), including derating VPIVOUT2F 1.00 0.0 V Output2 Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2C 1.00 0.0 V Output2 Catch Diode peak-inverse voltage (at VOVOFF_MAX), including derating VPIVB 1.00 N/A V Bias output rectifier peak-inverse voltage (at VDSOP), including derating	PD LOSS OUT2	1		0.00	W	
VPIVMAINF 1.00 206.5 V Main Forward Diode peak-inverse voltage (at VDSOP), including derating WPIVMAINC 1.00 152.2 V Main Catch Diode peak-inverse voltage (at VOVOFF_MAX), including derating VPIVOUT2F 1.00 0.0 V Output2 Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2C 1.00 0.0 V Output2 Catch Diode peak-inverse voltage (at VOVOFF_MAX), including derating VPIVOUT2C 1.00 N/A V Bias output rectifier peak-inverse voltage (at VDSOP), including derating		•				
VPIVMAINC 1.00 152.2 V Main Catch Diode peak-inverse voltage (at VOVOFF_MAX), including derating VPIVOUT2F 1.00 0.0 V Output2 Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2C 1.00 0.0 V Output2 Catch Diode peak-inverse voltage (at VOVOFF_MAX), including derating VPIVB 1.00 N/A V Bias output rectifier peak-inverse voltage (at VDSOP), including derating	VPIVMAINF	1.00		206.5	V	
VPIVOUT2F 1.00 0.0 V Output2 Forward Diode peak-inverse voltage (at VDSOP), including derating VPIVOUT2C 1.00 0.0 V Output2 Catch Diode peak-inverse voltage (at VOVOFF_MAX), including derating VPIVB 1.00 N/A V Bias output rectifier peak-inverse voltage (at VDSOP), including derating (at VDSOP), including derating	VPIVMAINC	1.00		152.2	V	Main Catch Diode peak-inverse voltage (at
VPIVOUT2C 1.00 0.0 V Output2 Catch Diode peak-inverse voltage (at VOVOFF_MAX), including derating VPIVB 1.00 N/A V Bias output rectifier peak-inverse voltage (at VDSOP), including derating	VPIVOUT2F	1.00		0.0	V	Output2 Forward Diode peak-inverse
VPIVB 1.00 N/A V Bias output rectifier peak-inverse voltage (at VDSOP), including derating	VPIVOUT2C	1.00		0.0	V	Output2 Catch Diode peak-inverse voltage
	VPIVB	1.00		N/A	V	Bias output rectifier peak-inverse voltage
	Hiner-TES STANDRY SECTI	ON (FLVBAC	K STAGE)		<u> </u>	(at 15501), including delating



ENTER APPLICATION VARI	ABLES				
VACMIN	90		90	V	Minimum AC Input Voltage
VACMAX	30		265	V	Maximum AC Input Voltage
fL			50	Hz	AC Mains Frequency
				V	
VO_SB			5.0	V	Output Voltage (at continuous power)
IO_SB	4.00		4.00	Α	Power Supply Output Current
					(corresponding to peak power)
IO_SB_PK			4.00	Α	Peak output current
POUT_SB			20.00	W	Continuous Output Power
POUT_SB_TOTAL			20.32	W	Total Standby power (Includes Bias winding
POUT_SB_TOTAL			20.32	VV	power)
POUT SB PK			20.32	W	Peak Standby Output Power
					Efficiency Estimate at output terminals.
n	0.75		0.75		Under 0.7 if no better data available
					Z Factor. Ratio of secondary side losses to
Z			0.50		the total losses in the power supply. Use
-			0.50		0.5 if no better data available
tC			3.00	mc	Bridge Rectifier Conduction Time Estimate
	 		3.00	ms	Bridge Rectifier Conduction Time Estimate
ENTER Hiper-TFS STANDBY	VARIABLE	S			
					Enter "LOW" for low current limit, "RED" for
			Increased		reduced current limit (sealed adapters),
Select Current Limit	INC		Current Limit		"STD" for standard current limit or "INC" for
			Current Linne		increased current limit (peak or higher
					power applications)
ILIM_MIN			0.70	Α	Minimum Current Limit
ILIM_TYP			0.75	Α	Typical Current Limit
ILIM MAX			0.80	Α	Maximum Current Limit
R(EN)			107	kΩ	Enable pin resistor
fSmin			124,000	Hz	Minimum Device Switching Frequency
1311111			127,000	112	
I^2fmin			66.8	A^2kHz	I^2f (product of current limit squared and
					frequency is trimmed for tighter tolerance)
VOR	110		110	V	Reflected Output Voltage (VOR < 135 V
-			_		Recommended)
VDS			10.0	V	Hiper-TFS Standby On State Drain to
155			1010	•	Source Voltage
VD_SB			0.5	V	Output Winding Diode Forward Voltage
VB_3B			0.5	V	Drop
KP			0.39		Ripple to Peak Current Ratio (KP < 6)
LCD TO ANIOTENIT			0.06		Transient Ripple to Peak Current Ratio.
KP_TRANSIENT			0.26		Ensure KP_TRANSIENT > 0.25
ENTER BIAS WINDING VAR	PLABLES				
VB		1	16.0	V	Bias Winding Voltage
	1				Bias winding Voltage Bias winding Load current
IB	1		20.0	mA	T
PB	ļ		0.32	W	Bias winding power
VDB	ļ		0.70	V	Bias Winding Diode Forward Voltage Drop
NB			12.1	turns	Bias Winding Number of Turns
VZOV	<u> </u>		22	٧	Over Voltage Protection zener diode
V2UV	<u> </u>		22	v	voltage.
UVLO VARIABLES					
			2.5-		Line sense resistor (from Main converter
RLS			3.97	ΜΩ	section)
V_UV_ACTUAL	1		101	V	Typical DC start-up voltage
ENTER TRANSFORMER COF	DE /CONSTD	LICTION VA		<u> </u>	Typical De Start up voltage
	1	OCTION VA			Entor Transformer Core
Core Type	EF25		EF25		Enter Transformer Core
AE	ļ		0.518	cm^2	Core Effective Cross Sectional Area
LE			5.78	cm	Core Effective Path Length
AL			2000	nH/T^2	Ungapped Core Effective Inductance
BW			15.6	mm	Bobbin Physical Winding Width
					Safety Margin Width (Half the Primary to
М			0	mm	Secondary Creepage Distance)
1	2.00		2		Number of Primary Layers
L	2.00				Number of Filliary Layers



NS SB	4	4		Number of Secondary Turns
DC INPUT VOLTAGE PARAN	· · · · · · · · · · · · · · · · · · ·	4		Number of Secondary Turns
VMIN_SB	ILTERS	78	V	Minimum DC Input Voltage
VMAX_SB	 	375	V	Maximum DC Input Voltage
CURRENT WAVEFORM SHA	PE PARAMETERS		<u> </u>	Tidximaiii De Inpat Voltage
				Duty Ratio at full load, minimum primary
DMAX_SB		0.62		inductance and minimum input voltage
IAVG		0.40	Α	Average Primary Current
IP_SB		0.70	Α	Minimum Peak Primary Current
IR_SB		0.27	Α	Primary Ripple Current
IRMS_SB		0.51	Α	Primary RMS Current
TRANSFORMER PRIMARY I	DESIGN PARAME	TERS	1	
LP_SB		1247	uH	Typical Primary Inductance. +/- 10% to ensure a minimum primary inductance of 1133 uH
LP_TOLERANCE		10	%	Primary inductance tolerance
NP_SB		80	turns	Primary Winding Number of Turns
ALG		195	nH/T^2	Gapped Core Effective Inductance
ВМ		2415	Gauss	Maximum Operating Flux Density, BM<3000 is recommended
BAC		469	Gauss	AC Flux Density for Core Loss Curves (0.5 X Peak to Peak)
ur		1776		Relative Permeability of Ungapped Core
LG		0.30	mm	Gap Length (Lg > 0.1 mm)
BWE		31.2	mm	Effective Bobbin Width
OD		0.39	mm	Maximum Primary Wire Diameter including insulation
INS		0.06	mm	Estimated Total Insulation Thickness (= 2 * film thickness)
DIA		0.33	mm	Bare conductor diameter
AWG		28	AWG	Primary Wire Gauge (Rounded to next smaller standard AWG value)
СМ		161	Cmils	Bare conductor effective area in circular mils
СМА		314	Cmils/Amp	Primary Winding Current Capacity (200 < CMA < 500)
TRANSFORMER SECONDAR	Y DESIGN PARA	METERS		
Lumped parameters		1		I
ISP	 	14.0	A	Peak Secondary Current
ISRMS IRIPPLE	 	8.07 7.01	A	Secondary RMS Current
IRIPPLE		7.01	Α	Output Capacitor RMS Ripple Current Secondary Bare Conductor minimum
CMS		1614	Cmils	circular mils
AWGS		18	AWG	Secondary Wire Gauge (Rounded up to next larger standard AWG value)
VOLTAGE STRESS PARAME	TERS	+		
VDRAIN		626	V	Maximum Drain Voltage Estimate (Assumes 20% zener clamp tolerance and an additional 10% temperature tolerance)
PIVS		24	V	Output Rectifier Maximum Peak Inverse Voltage
Forward DC-DC System eff	iciency			
P_MOSFET_MAIN_TOTAL		5.25	W	HiperTFS losses
P_XFMR_LOSS	 	3.2	W	Main transformer losses
P_MAIN_OUT_DIODE	 	2.3	W	Output diode losses
P_CIN_ESR	 	0.24	W	Bulk capacitor ESR losses
P_IND_MAIN	 	2.3	W	Output choke losses
OTHER_LOSSES		0.13	W	Other losses (includes PCB traces, clamp loss, magamp loss etc.)
EFFICIENCY_STDBY	 	75.0%		Estimated efficiency of flyback power supply
EFFICIENCY_MAIN		95.4%		Estimated Forward efficiency



EFFICIENCY_SYSTEM		93.7%	Estimated System efficiency (forward + standby)
Other Losses			
Detailed Mosfet Loss			
Information			

Note: PIXIs for TFS2 generates a "warning" message if the output inductor KDI_ACTUAL is ≥ 0.5 . This is still rather continuous, and the only real consequence of less continuous operation is slightly higher peak primary current, somewhat higher AC loss in the output inductor, and slightly higher ripple current in the output capacitors than would be the case in a more continuous design (lower KDI_ACTUAL). None of these factors posed significant issues in this design. A more continuous design would require more inductor turns or a larger core.

11 Heat Sinks

11.1 Main Primary Heat Sink (U1 and BR1)

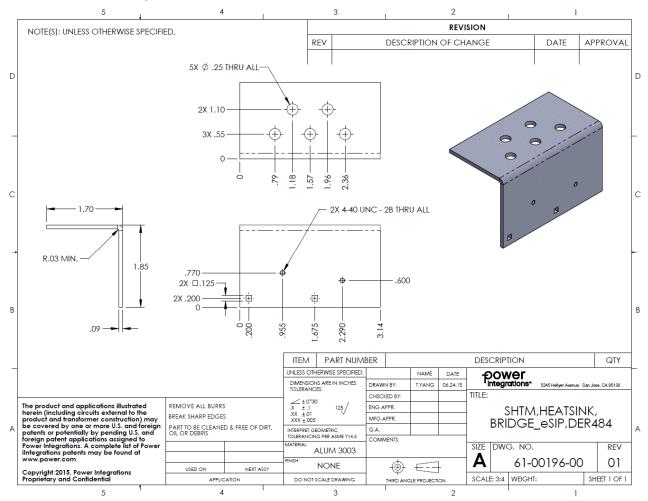


Figure 15 - U1/BR1 Heat Sink Sheet Metal.

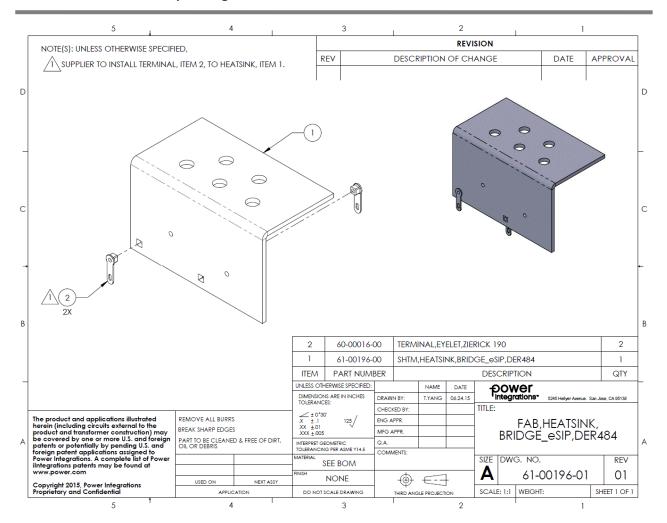


Figure 16 - U1/BR1 Completed Heat Sink.

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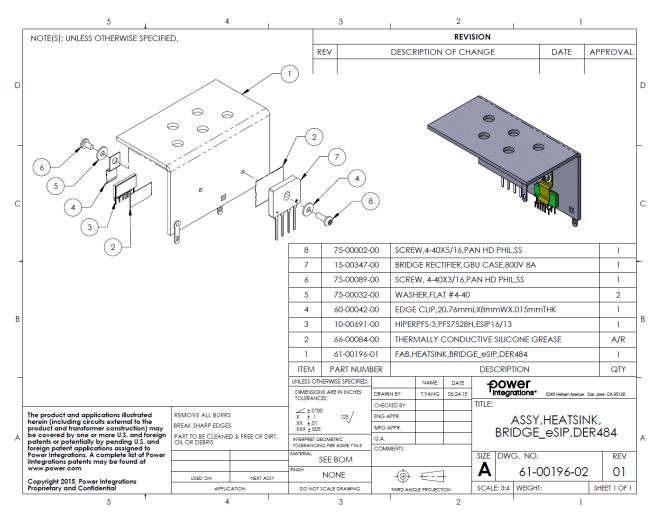


Figure 17 - U1/BR1 Heat Sink Assembly.

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11.2 Primary Heat Sink #2 (U2)

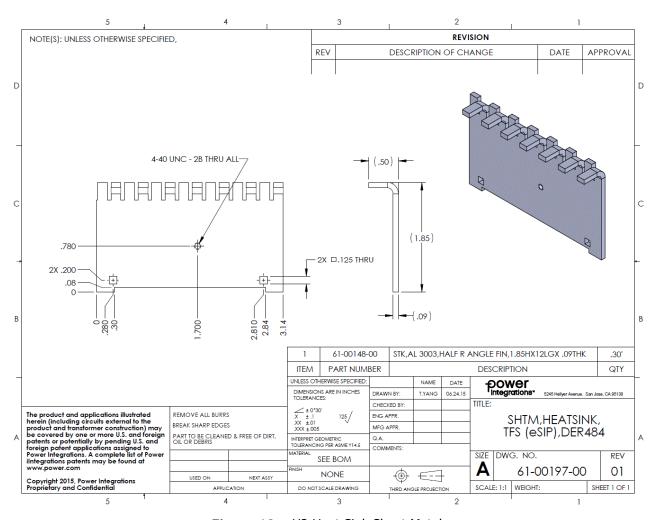


Figure 18 – U2 Heat Sink Sheet Metal.

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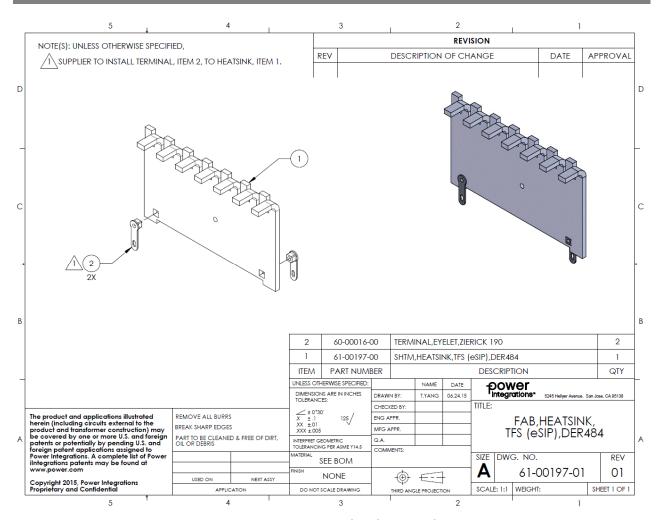


Figure 19 - U2 Completed Heat Sink.

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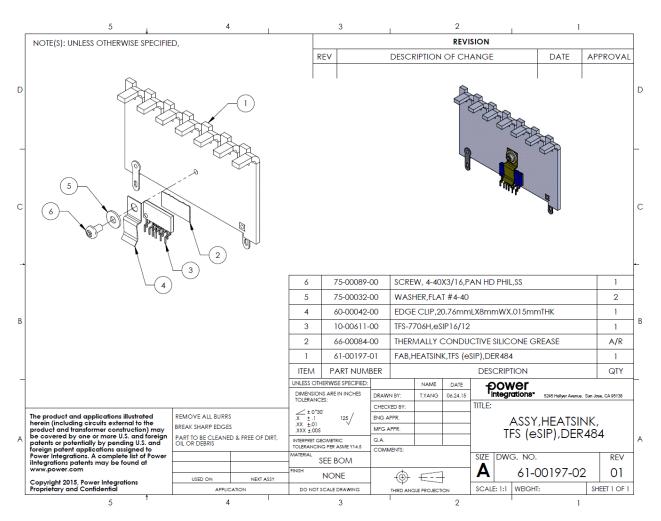


Figure 20 – U2 Heat Sink Assembly.

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REVISION NOTE(S): UNLESS OTHERWISE SPECIFIED, DESCRIPTION OF CHANGE APPROVAL REV D 2X 4-40 UNC - 2B THRU ALL-(.50) (1.85)2X .660 -- 2X □.125 THRU ф: 2X .200 0 -(.09) 2.850 В 61-00148-00 STK,AL 3003,HALF R ANGLE FIN,1.85HX12LGX .09THK .30' PART NUMBER QTY ITEM DESCRIPTION UNLESS OTHERWISE SPECIFIED: Power integrations NAME DATE DIMENSIONS ARE IN INCHES TOLERANCES: DRAWN BY: T.YANG 06.24.15 TITLE: CHECKED BY: ± 0°30' X ± .1 XX ±.01 XXX ±.005 The product and applications illustrated herein (including circuits external to the product and transformer construction) may be covered by one or more U.S. and foreign patents or potentially by pending U.S. and foreign patent applications assigned to Power Integrations. A complete list of Power integrations as on patent applications as on patentially assigned to the product of REMOVE ALL BURRS 125/ ENG APPR. SHTM, HEATSINK, BREAK SHARP EDGES DIODES, DER 484 PART TO BE CLEANED & FREE OF DIRT, OIL OR DEBRIS INTERPRET GEOMETRIC TOLERANCING PER ASME Y14.5 SIZE DWG. NO. REV SEE BOM Α 61-00198-00 01 NONE **(** SHEET 1 OF 1 DO NOT SCALE DRAW

11.3 Secondary Heat Sink

Figure 21 – Secondary Heat Sink Sheet Metal.



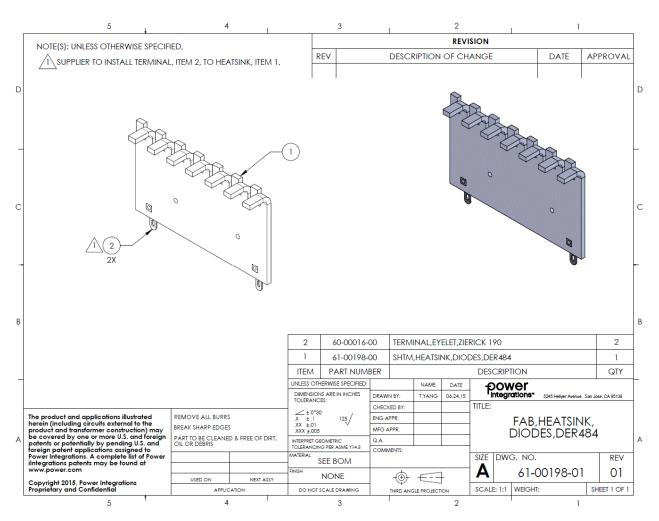


Figure 22 - Secondary Heat Sink (Completed).

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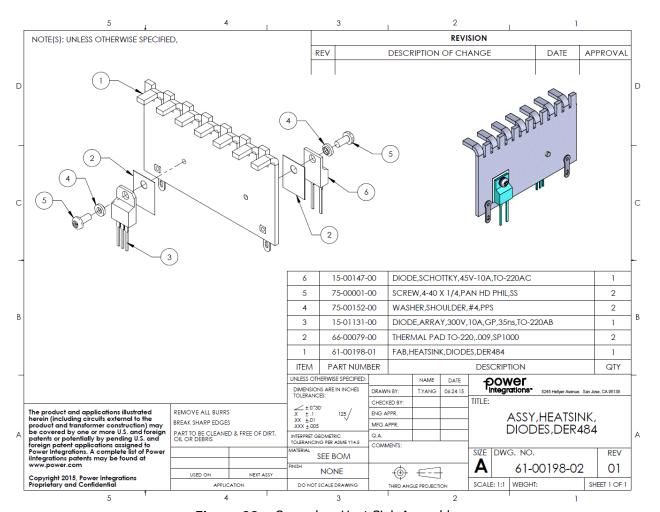


Figure 23 – Secondary Heat Sink Assembly.

12 Performance Data

All measurements were taken at room temperature and 60 Hz (input frequency) unless otherwise specified. Output voltage measurements were taken at the output connectors.

12.1 Output Load Considerations for Testing a CV/CC Supply in Battery Charger Applications

Since this power supply has a constant voltage/constant current output and normally operates in CC mode in its intended application (battery charging), some care must be taken in selecting the type/s of output load for testing.

The default setting for most electronic loads is constant current. This setting can be used in testing a CV/CC supply in the CV portion of its load range below the power supply current limit set point. Once the current limit of the DUT is reached, a constant current load will cause the output voltage of the DUT to immediately collapse to the minimum voltage capability of the electronic load.

To test a CV/CC supply in both its CV and CC regions (an example - obtaining a V-I characteristic curve that spans both the CV and CC regions of operation), an electronic load set for constant resistance can be used. However, in an application where the control loop is strongly affected by the output impedance, use of a CR load will give results for loop compensation that are overly optimistic and will likely oscillate when tested with an actual low impedance battery load.

For final characterization and tuning the output control loops, a constant voltage load should be used.

Having said this, many electronic loads incorporate a constant voltage setting, but the output impedance of the load in this setting may not be sufficiently low to successfully emulate a real-world battery (impedance on the order of tens of milliohms). Simulating this impedance can be crucial in properly setting the compensation of the current control loop in order to prevent oscillation in a real-life application.

12.2 Efficiency

To make this measurement, the supply was powered with an AC source. The figure shown includes the efficiency of the main forward stage combined with that of the standby/bias flyback supply.

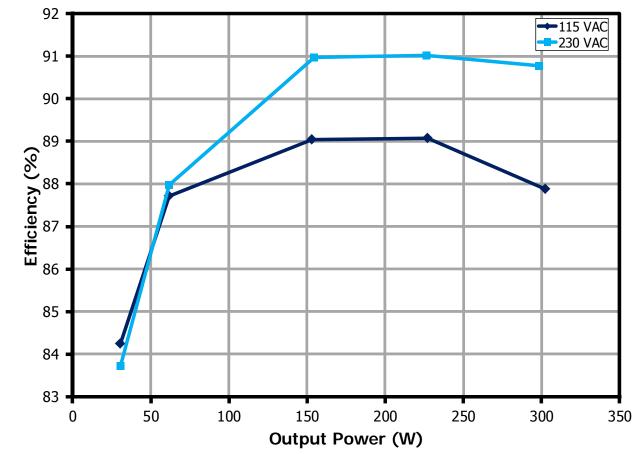


Figure 24 – Efficiency vs. Output Power.

12.3 No-Load Input Power

No-load input power was measured with no load on the main and standby outputs and with the main enable switch turned off, such that only the standby supply remained active.

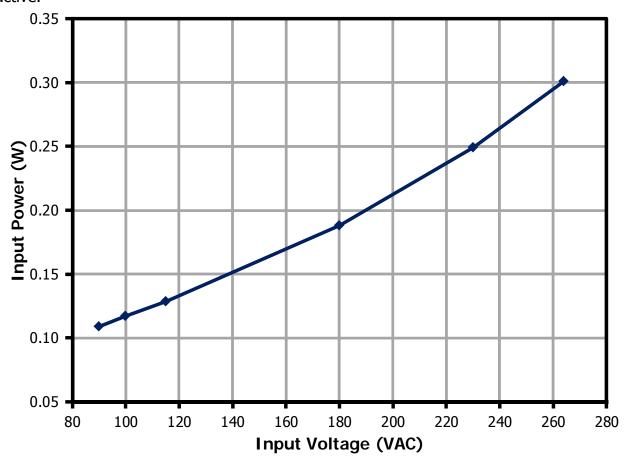


Figure 25 - No-Load Input Power vs. Input Voltage.

12.4 Power Factor

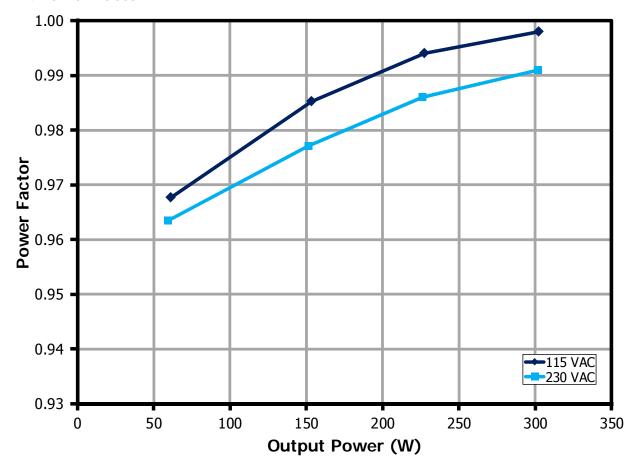


Figure 26 – Power Factor vs. Output Power.

12.5 Main Output V-I Characteristic

The main output V-I characteristic showing the transition from constant voltage mode to constant current mode was measured using a Chroma electronic load set for constant resistance. This setting allows proper operation of the DUT in both CV and CC mode. The measurements cut off at 3.2 V, as this is the minimum load voltage attainable by the electronic load in CR mode.

12.5.1 V-I Characteristic, Constant Resistance Load

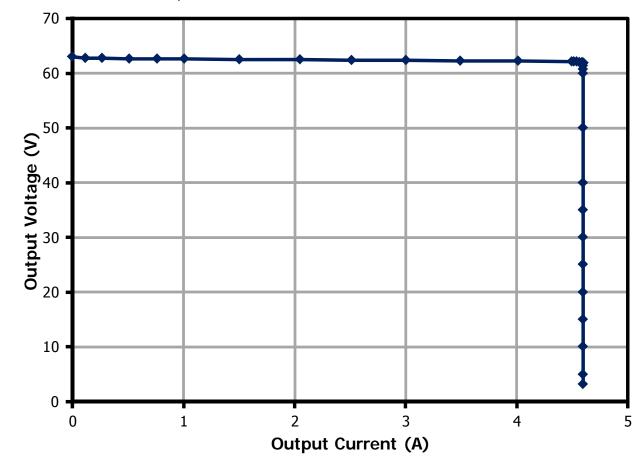


Figure 27 – V-I Characteristic with CR Load.

12.5.2 Main Output V-I Characteristic, Constant Voltage Load

The main output V-I characteristic in constant current mode was measured using a Chroma electronic load set for constant voltage mode. The minimum operating voltage of the load in CV mode is ~ 0.37 V.

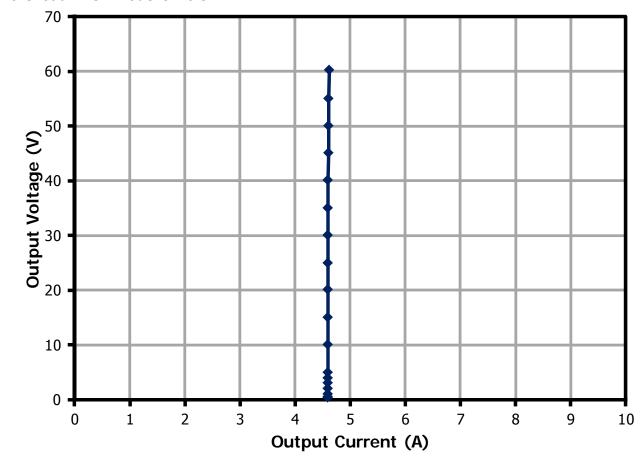


Figure 28 – V-I Characteristic with CV Load.

13 Waveforms

13.1 Primary Voltage and Current, Main and Standby Converters

The main stage primary current was measured by inserting a current sensing loop in series with the "HS" pin of U1.

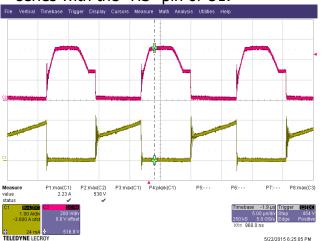


Figure 29 – Main Stage Primary Voltage and Current, 115 VAC Input, 100% Load.

Upper: D Pin Voltage, 200 V / div. Lower: I_{DRAIN} , 1 A / div., 5 μs / div.

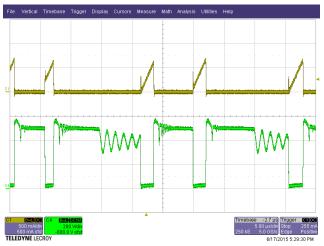


Figure 30 – Standby Primary Voltage and Current, 115 VAC Input, 100% Load Enable Switch "On".

Upper: I_{DRAIN}, 0.5 A /div.

Lower: DSB Pin Voltage, 200 V, 5 µs / div.

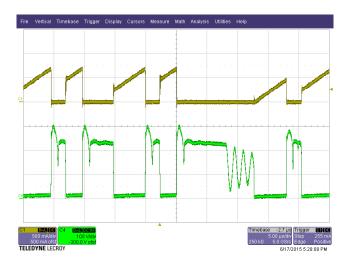


Figure 31 – Standby Primary Voltage and Current, 90 VAC Input, 100% Load, Enable Switch "Off".

Upper: I_{DRAIN}, 0.5 A / div.

Lower: DSB Pin Voltage, 100 V, 5 μs / div.



13.2 AC Input Voltage and Current

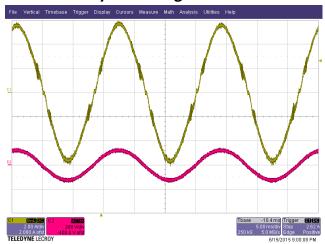


Figure 32 - AC Input Voltage and Current, 90 VAC, 100% Load.

Upper: AC I_{IN} , 2 A / div.

Lower: AC $V_{\rm IN}$, 200 V / 5 ms / div.

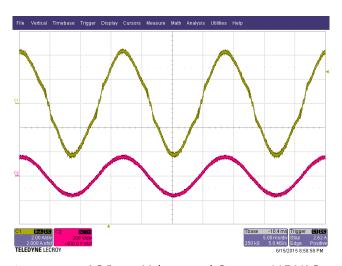


Figure 33 - AC Input Voltage and Current, 115 VAC, 100% Load.

Upper: AC I_{IN} , 2 A / div.

Lower: AC V_{IN} , 200 V / 5 ms / div.

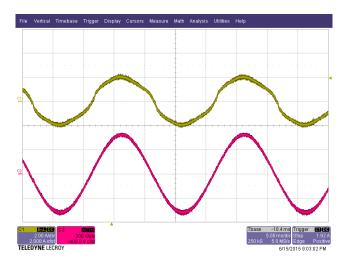


Figure 34 - AC Input Voltage and Current, 230 VAC, 100% Load.

Upper: AC I_{IN}, 2 A / div.

Lower: AC V_{IN} , 200 V / 5 ms / div.

13.3 PFC Stage Inductor Current / Drain Voltage Waveforms

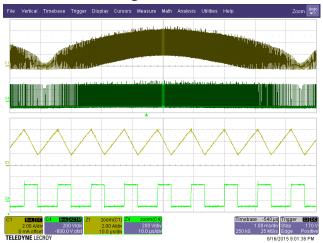


Figure 35 – PFC Inductor Current / Drain Voltage, 115 VAC, 100% Load.

Upper: $I_{INDUCTOR}$, 2 A / div.

Lower: V_{DRAIN} , 200 V / div., 1 ms / div. Zoom Upper: $I_{INDUCTOR}$, 2 A / div. Zoom Lower: V_{DRAIN} , 200 V / div.,

 $20 \mu s / div$.



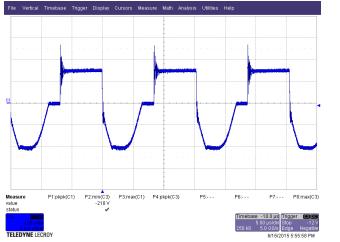
Figure 36 – PFC Inductor Current / Drain Voltage, 230 VAC, 100% Load.

Upper: I_{INDUCTOR} , 2 A / div.

Lower: V_{DRAIN} , 200 V / div., 1 ms / div. Zoom Upper: $I_{INDUCTOR}$, 2 A / div. Zoom Lower: V_{DRAIN} , 200 V / div.,

 $20 \mu s / div$.

13.4 Output Rectifier Peak Reverse Voltage



Measure P1:pkpk(C1) P2:max(C3) P3:max(C1) P4:pkpk(C3) P5:... P6:... P7:... P8:max(C3) status

Timebase 10:92 fideport (C3) status

Timebase 10:92 fideport (C3)

Figure 37 – Output Forward Rectifier (D19) Reverse Voltage, 115 VAC input, 100% Load. 100 V, 5 μs / div.

Figure 38 – Output Catch Rectifier (D19) Reverse Voltage, Leading Edge Spike, 115 VAC, 100% Load. 100 V, $5~\mu s$ / div.

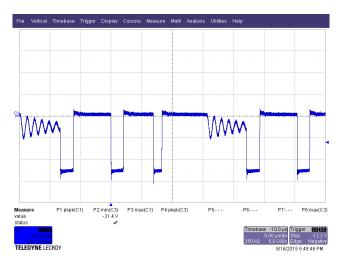


Figure 39 – Standby Output Rectifier (D18) Reverse Voltage, 115 VAC, 100% Load. 10 V, $5 \mu s$ / div.

13.5 Main Start-up Output Voltage / Current and Transformer Primary Current Using Constant Voltage and Constant Voltage Output Loads

13.5.1 Main and Standby Start-Up, Supply Started via AC Input

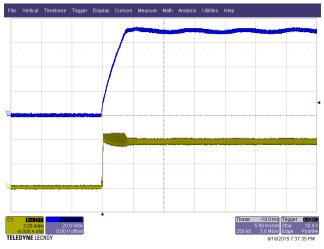


Figure 40 – Main Output Start-up, CV Mode, 115 VAC, Chroma CC Load, 4.3 A Setting. Upper: Main V_{OUT}, 10 V / div. Lower: Main I_{OUT}, 2 A, 2 ms / div.

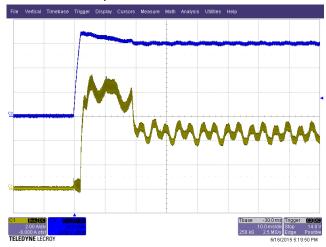


Figure 41 – Main Output Start-up, CC Mode, 115 VAC, Chroma CV Load, 60 V Setting. Upper: Main V_{OUT}, 20 V / div. Lower: Main I_{OUT}, 2 A, 10 ms / div.

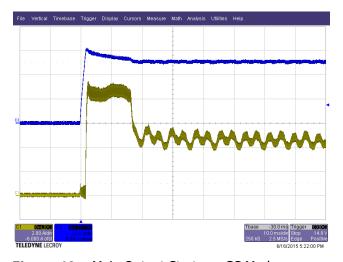


Figure 42 – Main Output Start-up, CC Mode, 115 VAC, Chroma CV Load, 50 V Setting. Upper: Main V_{OUT}, 20 V.

Lower: Main I_{OUT}, 2 A, 10 ms / div.

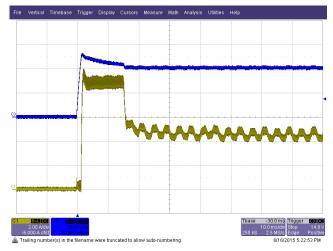
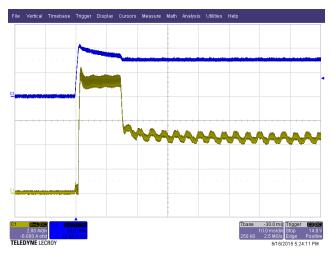


Figure 43 – Main Output Start-up, CC Mode, 115 VAC, Chroma CV Load, 45 V Setting.

Upper: Main V_{OUT}, 20 V.

Lower: Main I_{OUT} , 2 A, 10 ms / div.



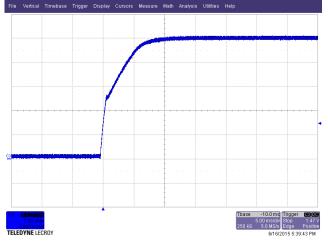


Figure 44 – Main Output Start-up, CC Mode. 115 VAC, Chroma CV Load, 30 V

Setting.

Upper: Main V_{OUT}, 20 V.

Lower: Main I_{OUT}, 2 A, 10 ms / div.

Figure 45 – Standby Start-up, 100% Load, 115 VAC Input, 1 V / 5 ms / div.

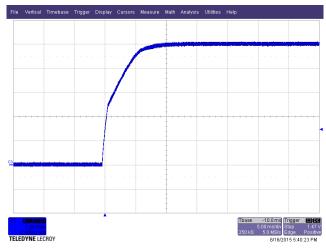


Figure 46 - Standby Start-up, No-Load, 115 VAC Input, 1 V / 5 ms / div.

13.5.2 Main Output Start-Up Using Enable Switch

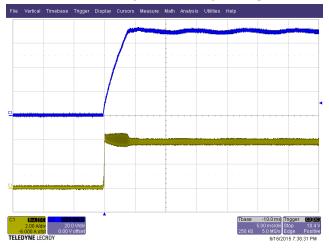


Figure 47 – Main Output Start-up, CV Mode, 115 VAC, Chroma CC Load, ~4.2 A Setting.

Upper: Main V_{OUT}, 20 V.

Lower: Main I_{OUT} , 2 A, 10 ms / div.

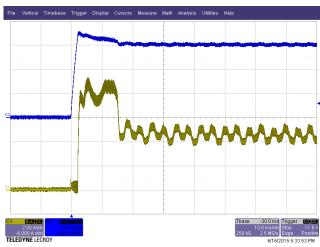


Figure 48 – Main Output Start-up, CC Mode, 115 VAC, Chroma CV Load, 60 V Setting. Upper: Main V_{OUT} , 20 V. Lower: Main I_{OUT} , 2 A, 10 ms / div.

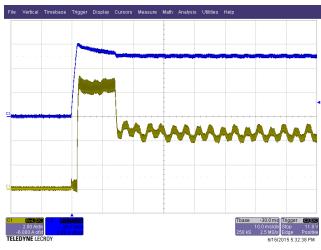


Figure 49 – Main Output Start-up, CC Mode, 115 VAC, Chroma CV Load, 50 V Setting.

Upper: Main V_{OUT} 10 V / div. Lower: Main I_{OUT} , 2 A, 10 ms / div.

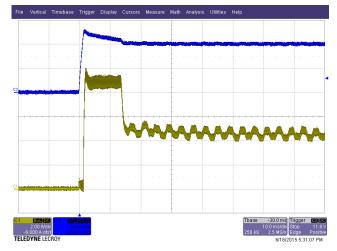


Figure 50 – Main Output Start-up, CC Mode, 115 VAC, Chroma CV Load, 40 V Setting. Upper: Main V_{OUT} 10 V / div

Lower: Main I_{OUT} , 2 A, 10 ms / div.

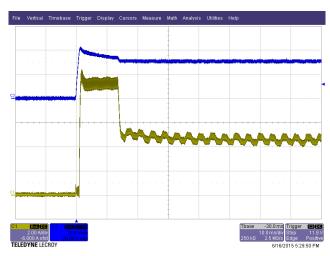


Figure 51 – Main Output Start-up, CC Mode, 115 VAC, Chroma CV Load, 30 V Setting.

Upper: Main V_{OUT} 10 V / div. Lower: Main I_{OUT} , 2 A, 10 ms / div.

13.6 Load Transient Response, Voltage Mode 50%-75%-50% Load Step

32 cycles of averaging were used on load transient waveforms to filter out ripple and better view actual output voltage excursion due to load transient.

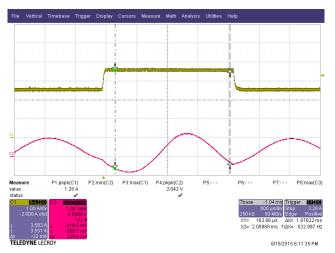


Figure 52 - Main Output Transient Response, CV Mode, 50%-75%-50% Load Step, 115 VAC Input. Upper: V_{OUT}, 200 mV / div.

Lower: Main Output I_{LOAD}, 1 A,

 $500 \mu s / div.$

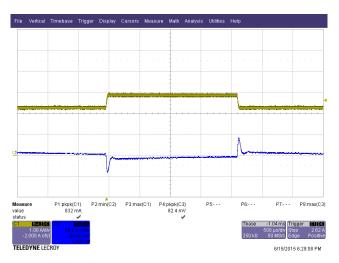


Figure 53 - Standby Output Transient Response, CV Mode, 50%-75%-50% Load Step, 115 VAC Input. Upper: V_{OUT} , 50 mV / div. Lower: Main Output I_{LOAD}, 1 A,

 $500 \mu s / div$.

14 Output Ripple Measurements

14.1 Ripple Measurement Technique

For DC output ripple measurements a modified oscilloscope test probe is used to reduce spurious signals. Details of the probe modification are provided in the figures below.

Tie two capacitors in parallel across the probe tip of the 4987BA probe adapter. Use a 0.1 μ F / 50 V ceramic capacitor and 10 μ F / 100 V aluminum electrolytic capacitor. The electrolytic capacitor is polarized, so always maintain proper polarity across DC outputs.

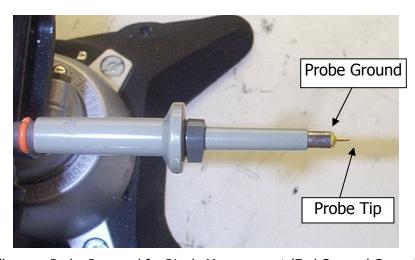


Figure 54 – Oscilloscope Probe Prepared for Ripple Measurement (End Cap and Ground Lead Removed).

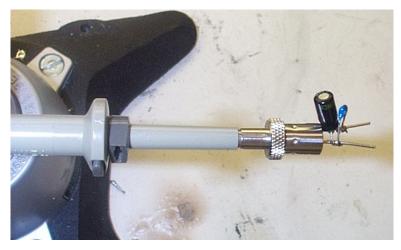


Figure 55 – Oscilloscope Probe with Probe Master 4987BA BNC Adapter (Modified with Wires for Probe Ground for Ripple measurement and Two Parallel Decoupling Capacitors Added).

14.2 Output Ripple Measurements

Measurements were taken for output ripple voltage with the main supply operating in constant voltage mode with a constant current load, and for both output ripple voltage and current with the main supply operating in CC mode. CC mode measurements were taken using a Chroma electronic load set in CV mode at 59 V, 50 V, and 40 V, and 30 V CV settings. Output ripple voltage/current measurements were made using AC coupled

voltage and/or current probes.

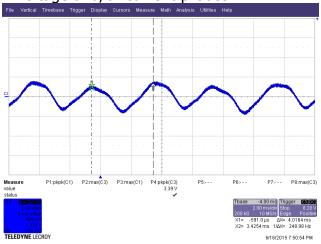


Figure 56 – Main Output Voltage Ripple, 115 VAC, CV Mode, 100% Load Using Chroma CR Load – 200 mV, 5 ms / div.

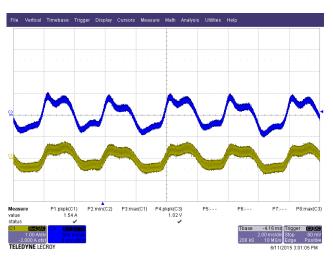


Figure 57 – Output Voltage and Current Ripple in CC Mode, 115 VAC, Chroma CV Load, 59 V Setting.

Upper: Main V_{OUT} Ripple, 1 V / div. Lower: I_{OUT} Ripple, 1 A, 2 ms / div.

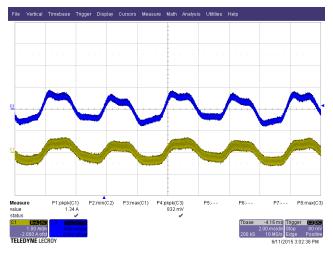


Figure 58 – Main Output Voltage and Current Ripple in CC Mode, 115 VAC, Chroma CV Load, 50 V Setting.

Upper: Main V_{OUT} Ripple, 1 V / div. Lower: I_{OUT} Ripple, 1 A, 2 ms / div.

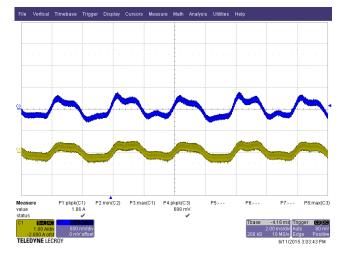


Figure 59 – Main Output Voltage and Current Ripple in CC Mode, 115 VAC, Chroma CV Load, 40 V Setting.

Upper: Main V_{OUT} Ripple, 1 V / div. Lower: I_{OUT} Ripple, 1 A, 2 ms /div.



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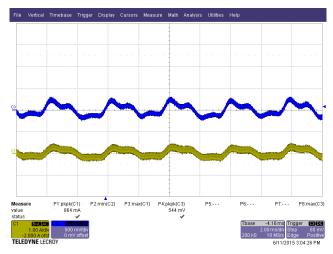


Figure 60 – Main Output Voltage and Current Ripple in CC Mode, 115 VAC, Chroma CV Load, 30 V Setting.

Upper: Main V_{OUT} Ripple, 1 V / div. Lower: I_{OUT} Ripple, 1 A, 2 ms / div.

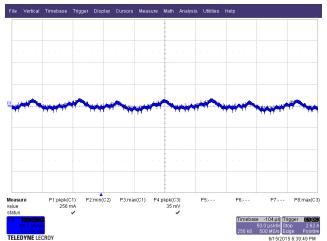


Figure 61 – Standby Output Voltage Ripple, 100% Load, 90 VAC with 100% Load on Main Output, Enable Switch "Off" - 100 mV, $100 \mu s / div.$

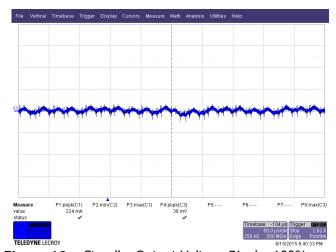


Figure 62 – Standby Output Voltage Ripple, 100% Load, 115 VAC, Main Output/PFC Enabled with ON/OFF Switch - 100 mV, $100 \mu s / div.$

15 Temperature Profiles

The board was operated at room temperature, with output set at maximum using a Chroma electronic load with constant resistance for the main output and constant current mode for the standby output. The constant resistance load for the main output allows the main load to be set for maximum power output without having the main output drift into current limit and collapsing the output voltage, as can happen when a constant current load is used. The unit was allowed to thermally stabilize before measurements were made.

This supply requires airflow, especially to reduce the temperature of the primary heat sink cooling the PFS3 (U10) and bridge rectifier BR1. An actual customer application will be sensitive to fan size, speed an placement. Figure 62 shows the fan placement for the measurements taken below. The fan location was offset somewhat to favor the heat sink for U10 and BR1.

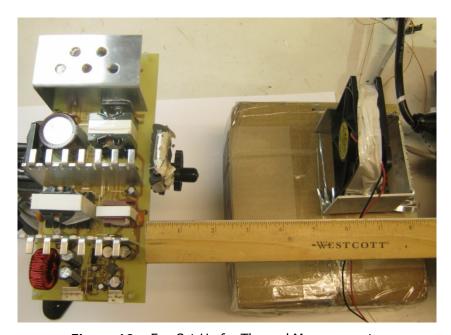


Figure 63 – Fan Set-Up for Thermal Measurements.

15.1 Spot Temperature Measurements

Position		Temperature (°C)	
	90 VAC	115 VAC	230 VAC
T1 (Main)	59.7	57.5	59.5
T2 (Standby)	35.7	35.9	35.3
BR1	66.3	53.7	35.4
L2 (CM)	57.4	46.3	35.4
L6 (DM)	37.6	31.4	23
L3 (Main)	63.2	63	63.4
L1 PFC Choke	45.3	39	30.2
U10	73.1	56.1	36.8
U2	36	39.1	38.6
D19 Main (FWD/CTH)	61.6	60.8	61.1
D18 Standby Rectifier	52	52.3	51
Ambient	21	21	21

15.1.1 90 VAC, 60 Hz, 100% Load Overall Temperature Profile

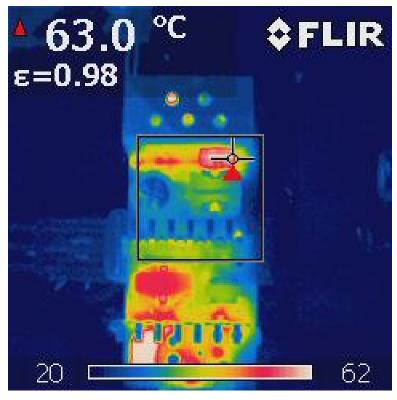


Figure 64 – Top View Thermal Picture, 90 VAC.

16 Gain-Phase

16.1 Main Output Constant Voltage Mode Gain-Phase

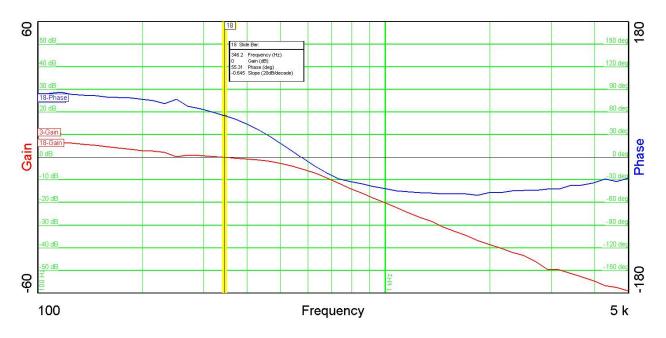


Figure 65 – Main Output Voltage Mode Gain-Phase Plot with Chroma CC Load - Gain Crossover is 346 Hz, Phase Margin is 55.3°.

16.2 Main Output Constant Current Mode Gain-Phase

Gain-phase was tested using a Chroma electronic load set to constant voltage mode at four set points – 59 V, 50 V, 40 V, and 30 V, obtaining the gain-phase measurements for several points on the V-I characteristic curve. Using a CV load maximizes the CC loop gain (worst case for control loop) and simulates operating while charging a low impedance load like a battery. Using the constant resistance setting for the electronic load will yield overly optimistic results for gain-phase measurements and for determining component values for frequency compensation.

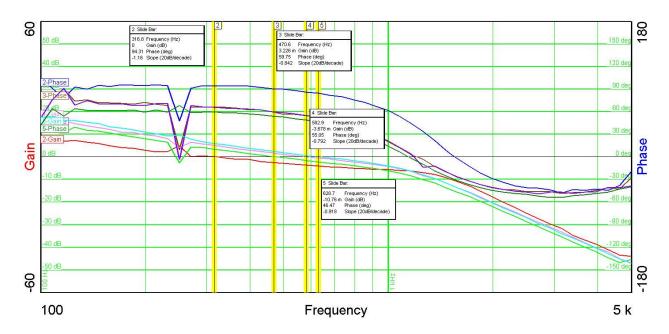


Figure 66 – Main Output Gain-Phase, Constant Current Output, Chroma Constant Voltage Load. Red/Blue – 59 V Gain and Phase Crossover Frequency – 317 Hz, Phase Margin – 94°. Brown/Green – 50 V Gain and Phase Crossover Frequency – 471 Hz, Phase Margin – 60°. Pink/Purple – 40 V Gain and Phase Crossover Frequency – 583 Hz, Phase Margin – 55°. Aqua/Dark Green – 30 V Gain and Phase Crossover Frequency – 629 Hz, Phase Margin – 46.5°.

17 Conducted EMI

Conducted EMI tests were performed using floating resistive loads (13 Ω main, 1.25 Ω standby). Physical set-up is shown in the figure below.

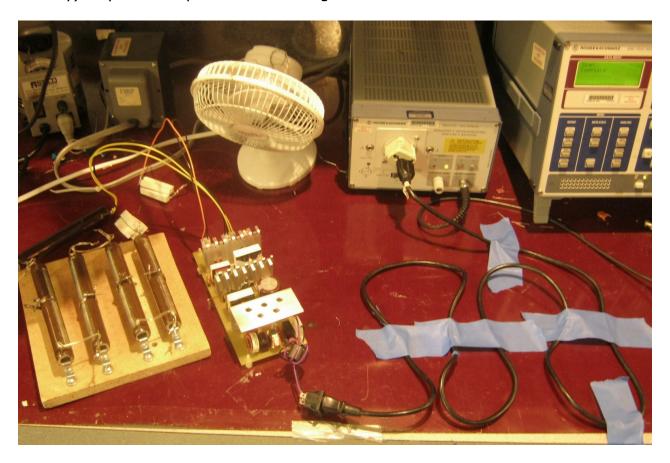


Figure 67 – Physical Setup for Conducted EMI Measurements.

A supplemental common mode choke was added to the AC input cable harness of the supply as shown in Figure 67. This choke consisted of 4 turns on a Fair-Rite 5943000201 toroidal bead. In practice, this choke would be wound into the AC input cord inside the power supply enclosure



Figure 68 – Supplemental CM Choke (4T on Fair-Rite 5943000201).



17.1 Conducted EMI Scan

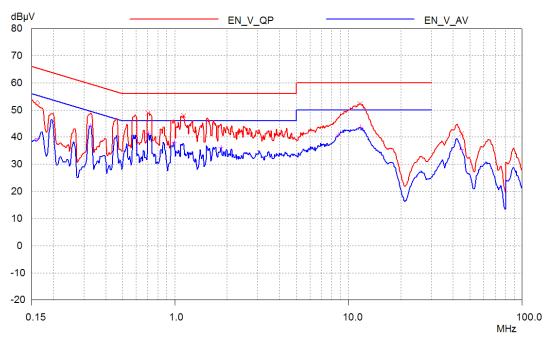


Figure 69 – Conducted EMI, 115 VAC, 13 Ω (Main) and 1.25 Ω (Standby) Floating Resistive Loads.

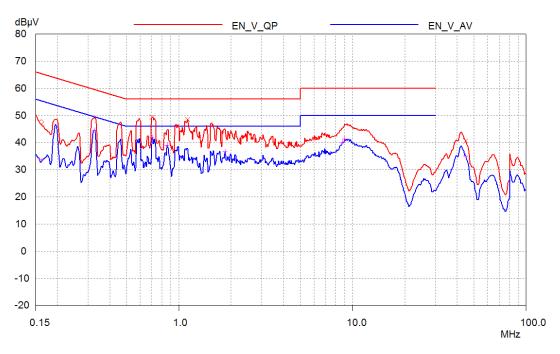


Figure 70 – Conducted EMI, 230 VAC, 13 Ω (Main) and 1.25 Ω (Standby) Floating Resistive Loads.

18 Revision History

Date	Author	Revision	Description & changes	Reviewed
06-Oct-15	RH	1.0	Initial Release	Apps & Mktg
16-Nov-15	KM	1.1	Updated Schematic.	
26-Nov-17	KM	1.2	Added Magnetics Supplier for L2, L3 L4, L5, T1 and T2.	

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